

Look Inside.™

Advancing Moore's Law on 2014!

Monday, August 11, 2014



Rani Borkar – Vice President, Platform Engineering Group

Rani leads the Product Development Group, and will present Intel's 14nm product development vision as manifest in the Broadwell microarchitecture.



Mark Bohr – Intel Senior Fellow, Logic Technology Development

Mark directs process architecture, development and Integration for Intel's advanced logic technologies, delivering staggering innovations in accord with Moore's Law.



Stephan Jourdan – Intel Fellow, Platform Engineering Group

Formerly chief architect of Broadwell, Stephan currently directs the definition and architectural development of Intel's SoCs for tablets and phones.

Risk Factors

Today's presentations contain forward-looking statements. All statements made that are not historical facts are subject to a number of risks and uncertainties, and actual results may differ materially. Please refer to our most recent earnings release, Form 10-Q and 10-K filing available for more information on the risk factors that could cause actual results to differ.

If we use any non-GAAP financial measures during the presentations, you will find on our website, intc.com, the required reconciliation to the most directly comparable GAAP financial measure



A Multi-Year Journey

Rani Borkar

Vice President, Product Development Group

August 11, 2014

14nm and Broadwell Micro-architecture

Enabling A Broad Spectrum of Leadership Products



A Multi-Year Journey to Re-invent the Notebook

What the Market Saw...

2010

Unveils New 2010
Intel® Core™
Processor Family



Intel® Core™
Processor

2011

Category
Introduction
Drive To Thin



2nd Generation
Intel® Core™
Processor

2012

Adding Touch



3rd Generation
Intel® Core™
Processor

2013

Ultrabook™ & 2 in 1



4th Generation
Intel® Core™
Processor

A Multi-Year Journey to Re-invent the Notebook

What Was Going On Under the Hood...

2010

**Westmere
32nm**

ULV processors
Turbo
Integrated Gfx on Package
Power Control Unit
Power Gates
Increased Parallelism &
Hyper-Threading

2011

**Sandy Bridge
32nm**

Integrated On-die Gfx
More Aggressive Turbo
Core/Gfx Power Balancing
Platform Power Limits
More efficient OoO Engine

2012

**Ivy Bridge
22nm**

22nm Tri-gate Transistor
Improved Perf at Low V
Configurable TDP
Increased 3D Gfx Perf
DirectX11 Support

2013

**Haswell
22nm**

ULT Process Optimization
2X Battery life
20X Idle power reduction
Chipset MCP Integration
Low Latency Idle States
New FIVR
Increased Dynamic
Operating Range

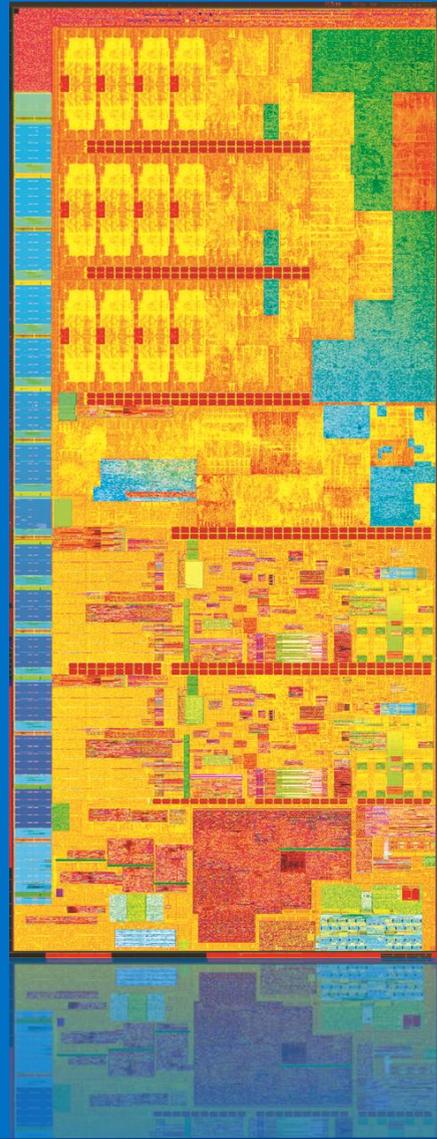
2014

**Broadwell-Y
14nm**



Intel® Core™ Processor Low Power Evolution

Coming Soon: Intel® Core™ M



- 14nm 2nd Gen Tri-Gate Transistors
- TDP Reduction Enabling ≤ 9 mm Fanless Designs
- System Optimized Dynamic Power & Thermal Management
- Reduction in SOC Idle Power & Increased Dynamic Operating Range
- 2nd Gen FIVR & 3DL Technology
- Next Gen Broadwell Converged Core
- Next Gen Graphics/Media/Display
- Chipset: Lower Power, Voice Usages, Faster Storage

*Delivering The Experience of Intel® Core™
In Fanless Form Factors*

A Multi-Year Journey to Re-invent the Notebook

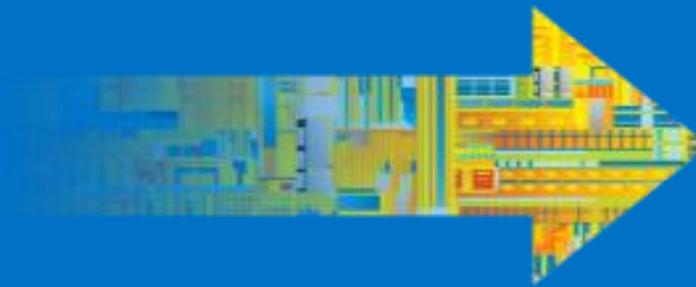
2010

What the Users Will Experience...

2014



Intel® Core™
Processor



Thickness: From 26mm to 7.2mm

TDP: 4X Reduction

Graphics: 7X Improvement

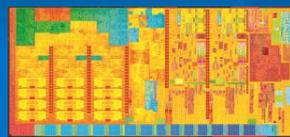
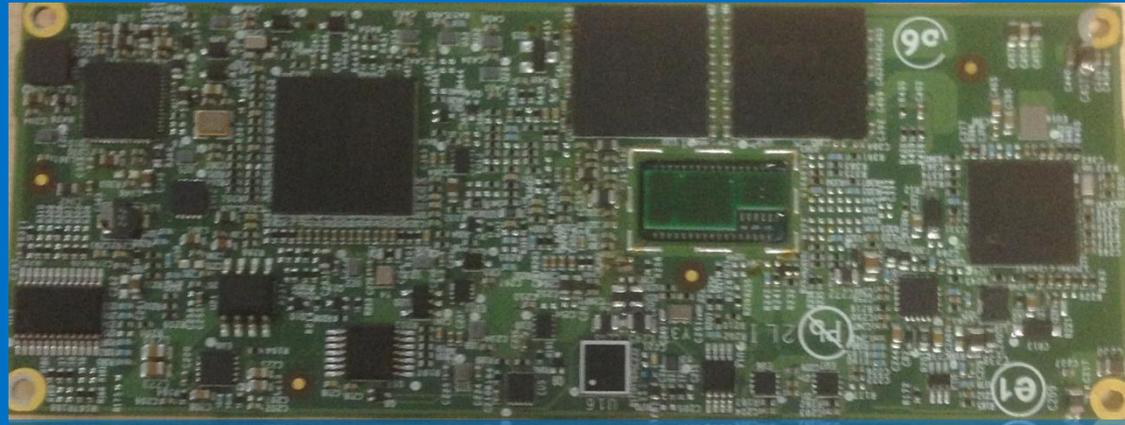
IA Core: 2X Improvement

1/2 the Battery Size & Double the Life



Intel® Core™ M

Outside-In System Design



Innovations Across the Stack

Packaging & Form Factor Optimizations

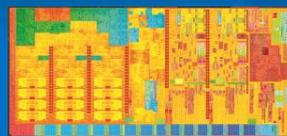
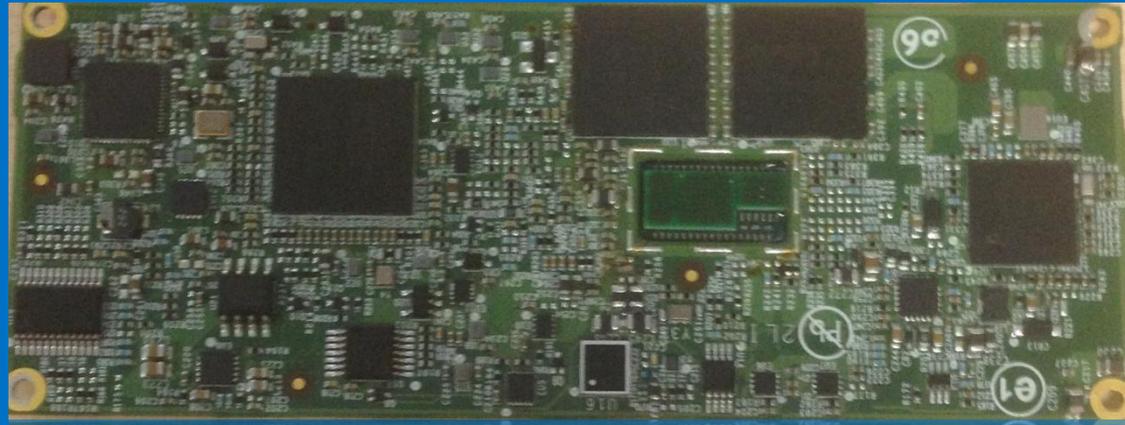
Efficient Power Delivery

Platform Power/Thermal Mgt.

SoC Power Reductions

14nm Process & Design Co-optimization

Outside-In System Design



Innovations Across the Stack

Enabled Board Area Reduction of ~25%
Compared to Haswell with 50% Smaller Package
2nd Gen FIVR & 3DL for Increased Power Delivery
Efficiency & Performance

Enhanced Turbo Boost, Increased Dynamic
Operating Range & System Optimized
Power/Thermal Management

Adopted Advanced Design Techniques for
Aggressive Power Reduction

14nm Design/Process Optimizations Delivered
2X Lower Power than Traditional Scaling

Intel® Core™ M Processor Improvements



Enables $\leq 9\text{mm}$ Fanless 2-in1's for the First Time on the Intel Core™ Roadmap



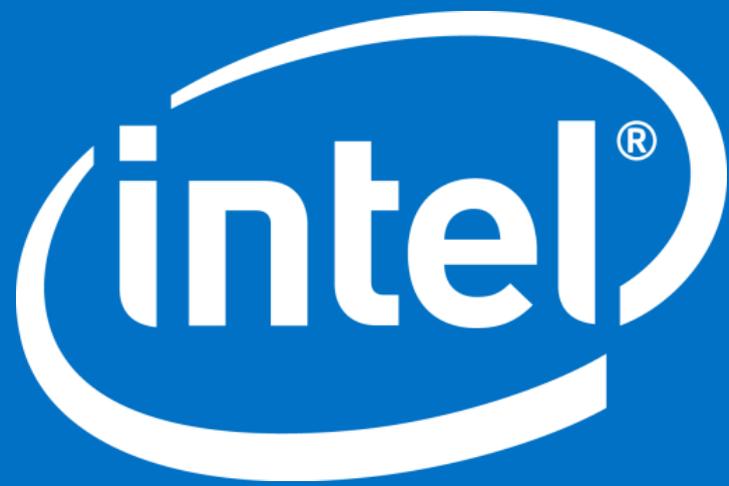
Greater than 2X reduction in TDP with better performance vs. Haswell-Y

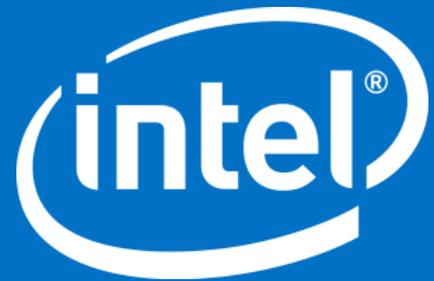


50% Smaller Package (XY), 30% Thinner



60% Lower SOC Idle Power for Increased Battery Life





14 nm Technology Announcement

Mark Bohr

Intel Senior Fellow

Logic Technology Development

August 11, 2014

Key Messages

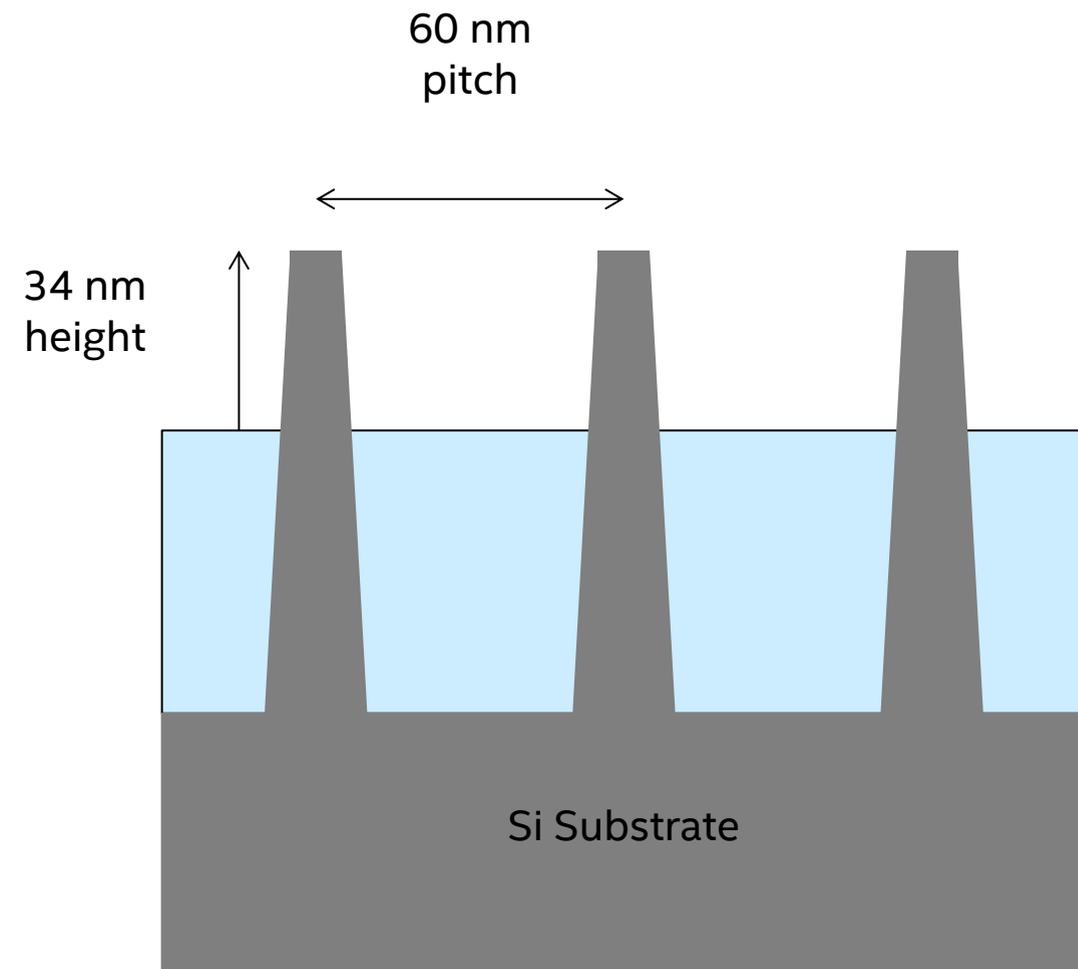
- Intel's 14 nm technology is now qualified and in volume production
- This technology uses 2nd generation Tri-gate (FinFET) transistors with industry-leading performance, power, density and cost per transistor
- The lead 14 nm product is a family of processors using the new Broadwell microarchitecture
- Intel's 14 nm technology will be used to manufacture a wide range of products, from high performance to low power

Minimum Feature Size

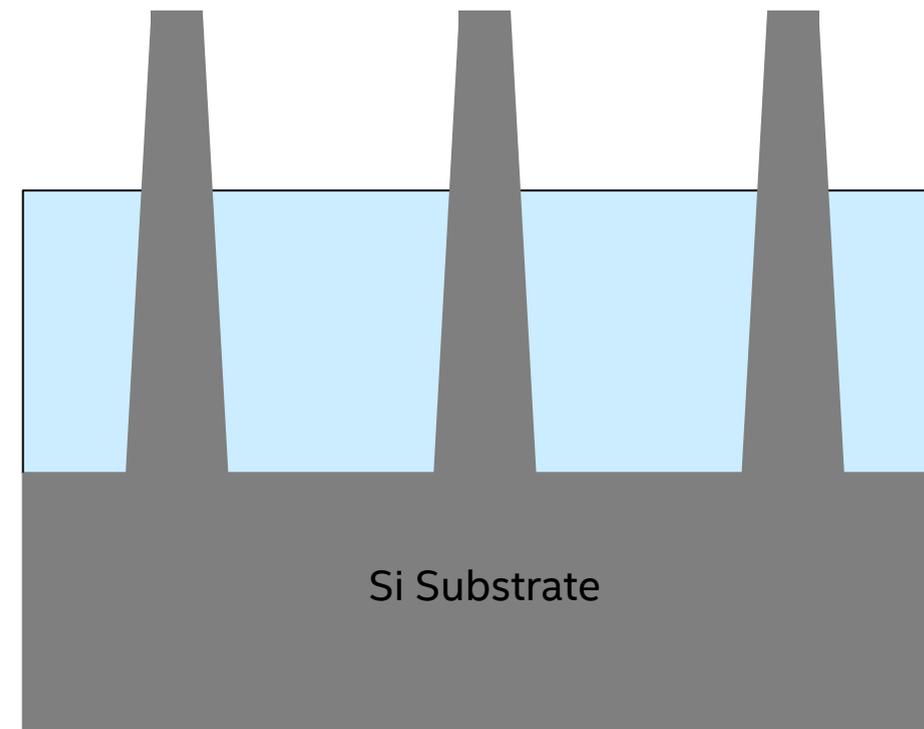
	22 nm Node	14 nm Node	Scale
Transistor Fin Pitch	60	42	.70x
Transistor Gate Pitch	90	70	.78x
Interconnect Pitch	80 nm	52 nm	.65x

*Intel Has Developed a True 14 nm Technology
with Good Dimensional Scaling*

Transistor Fin Improvement

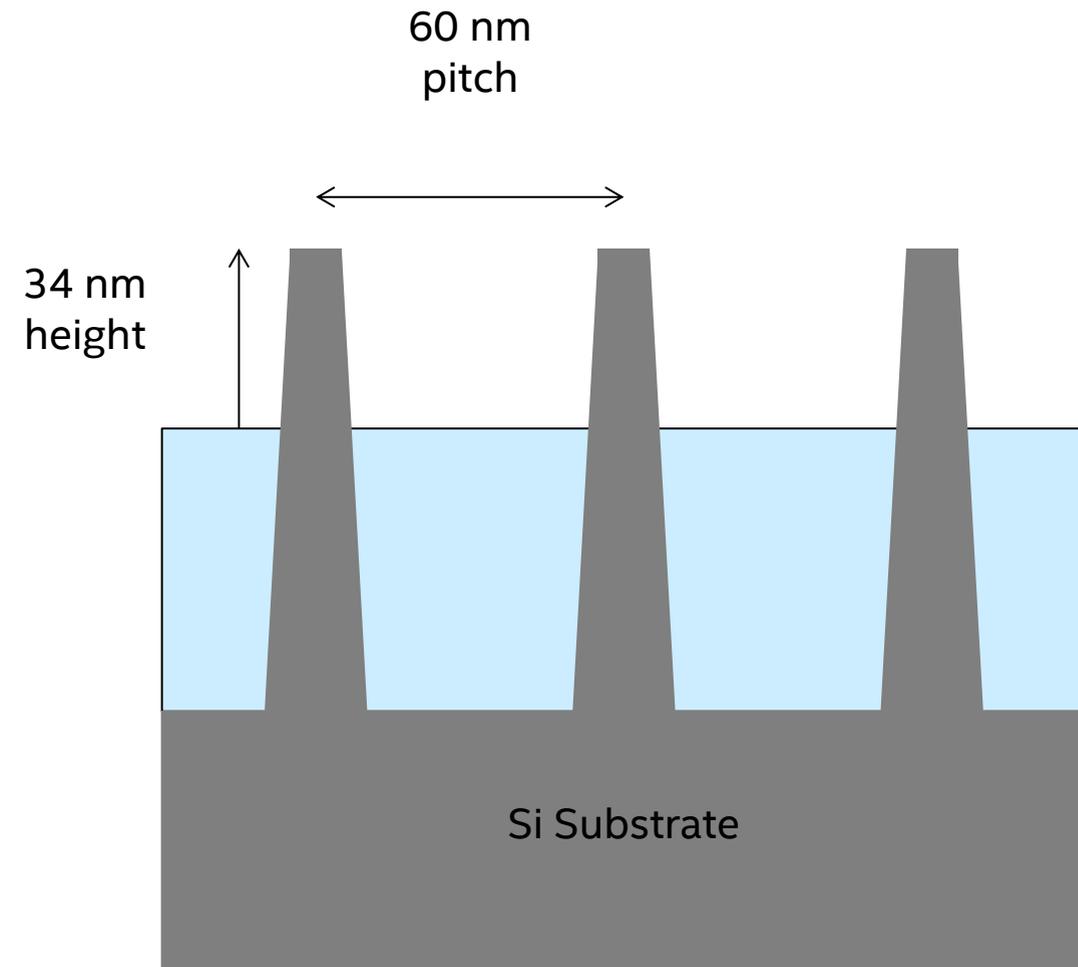


22 nm Process

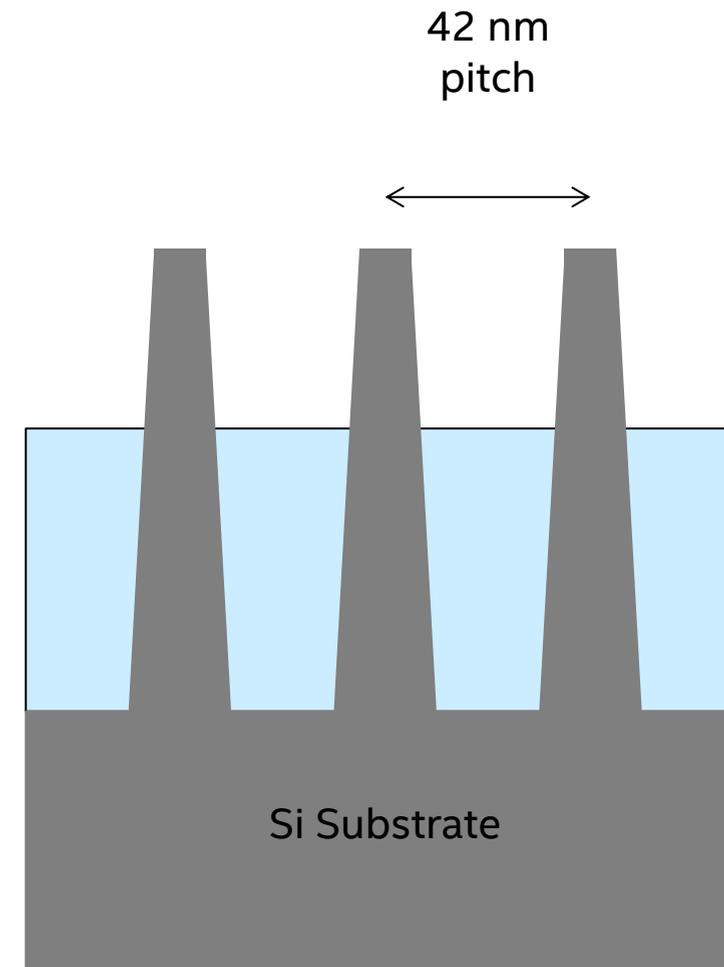


14 nm Process

Transistor Fin Improvement



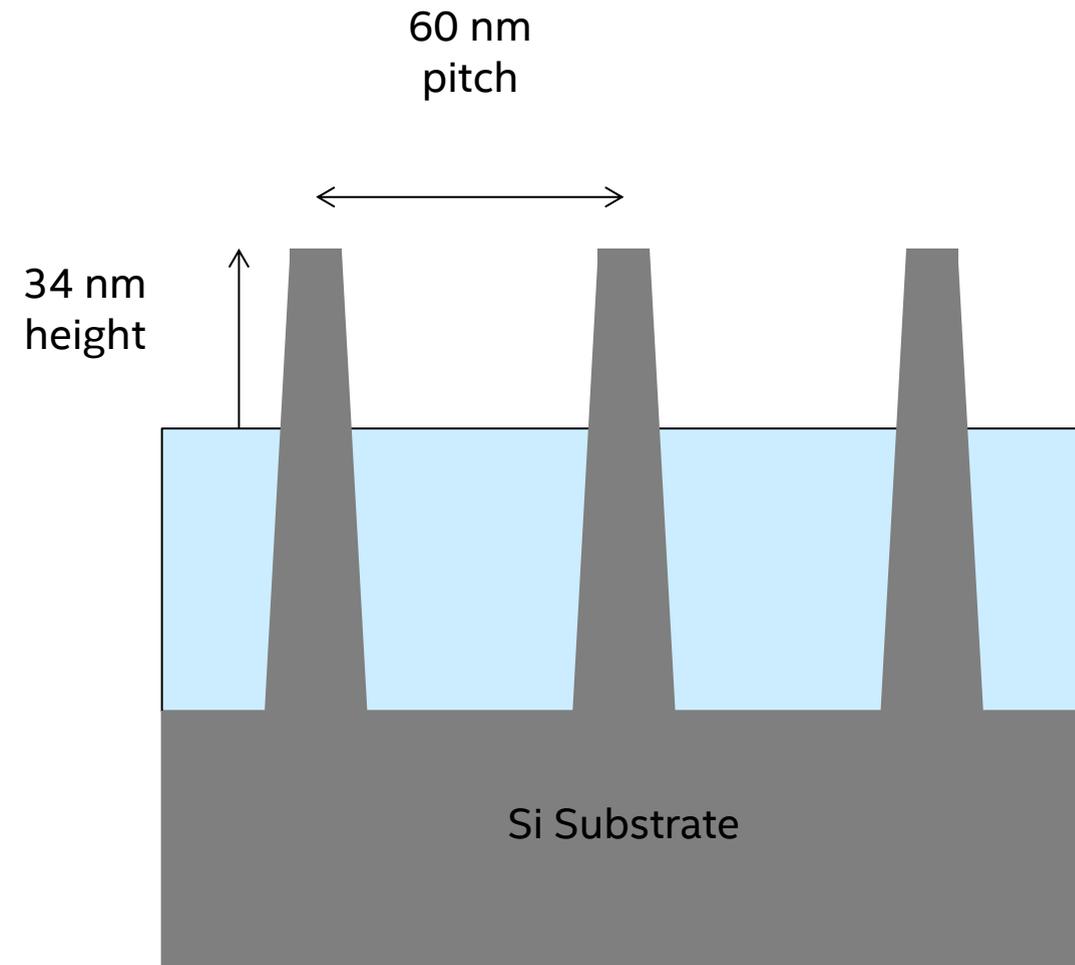
22 nm Process



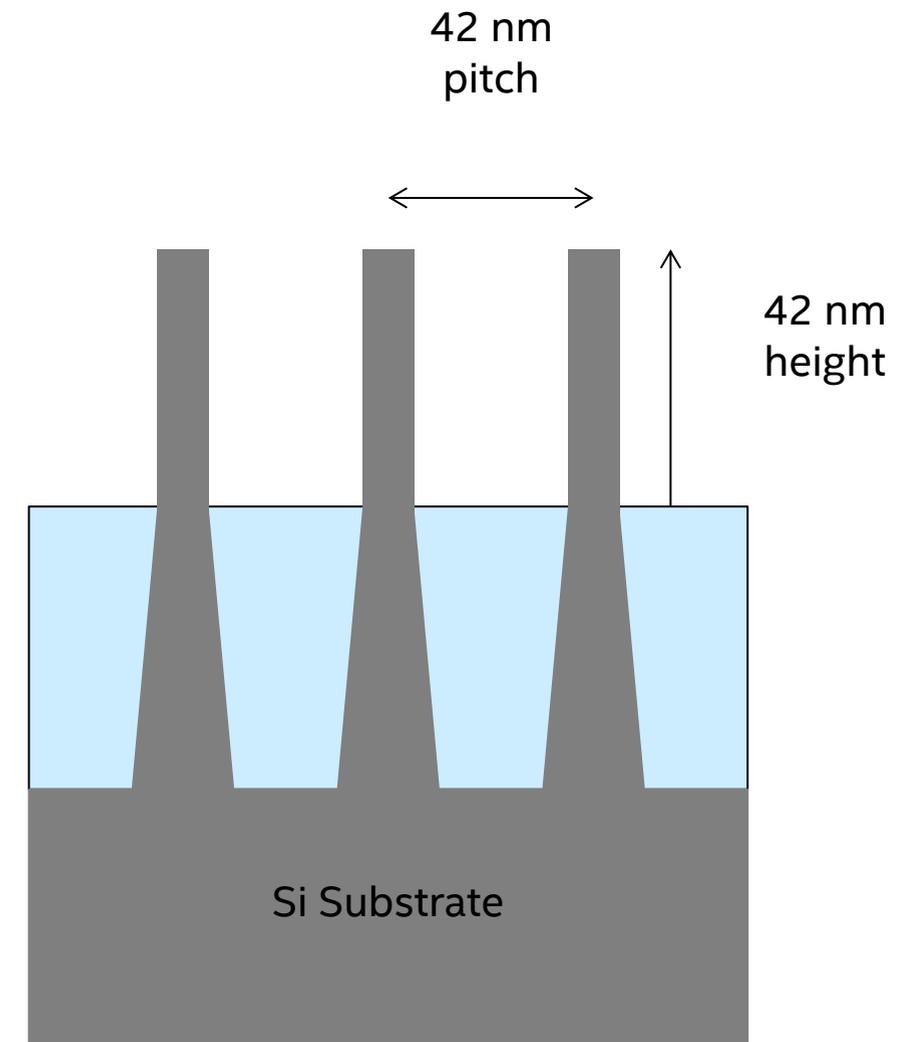
14 nm Process

Tighter Fin Pitch for Improved Density

Transistor Fin Improvement



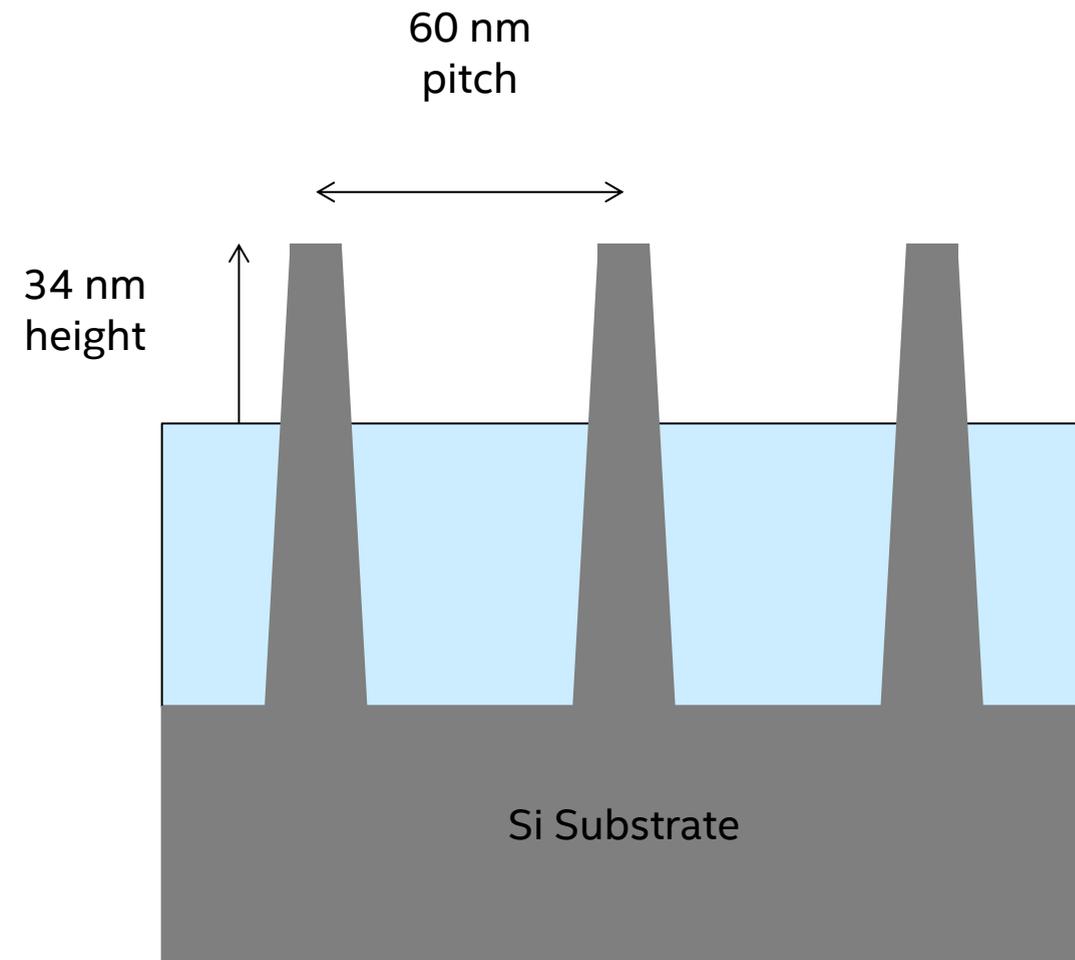
22 nm Process



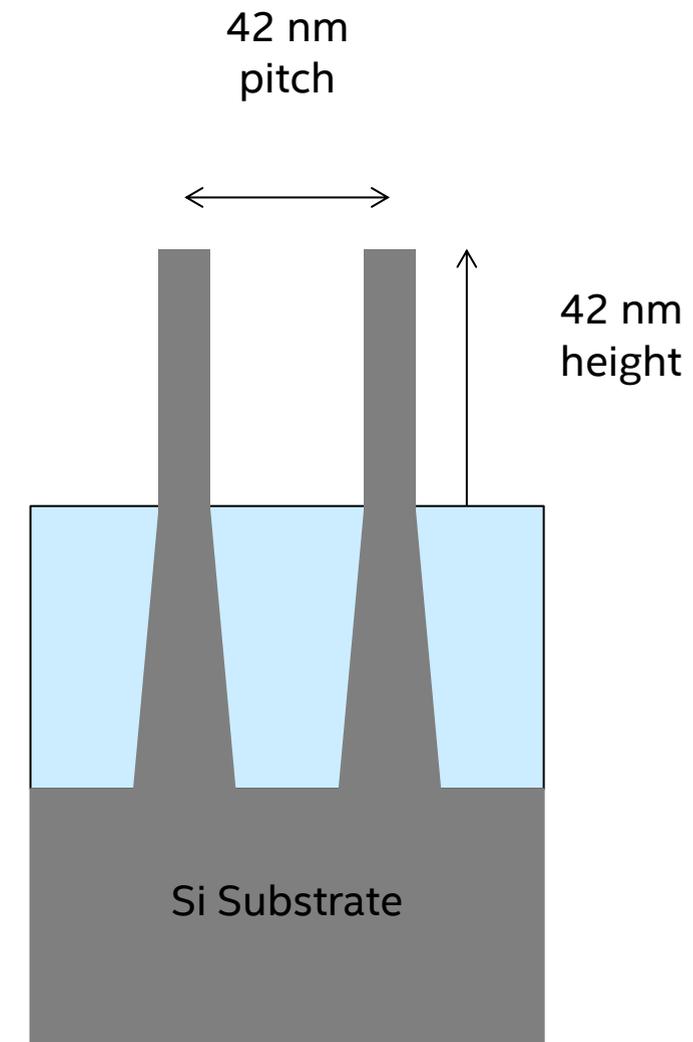
14 nm Process

Taller and Thinner Fins for Increased Drive Current and Performance

Transistor Fin Improvement



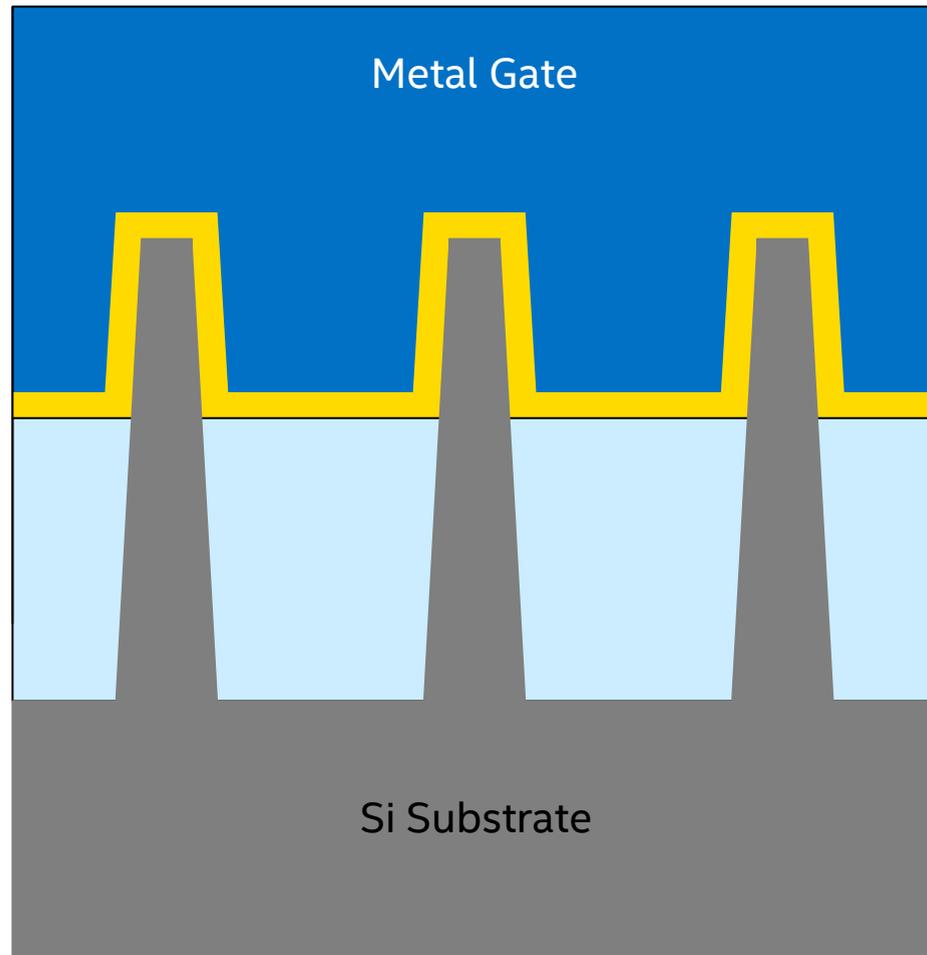
22 nm Process



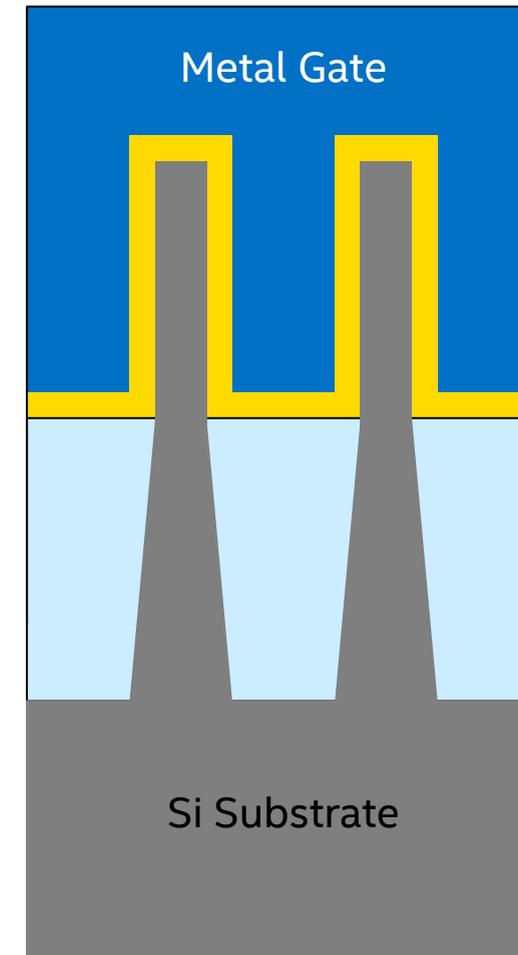
14 nm Process

Reduced Number of Fins for Improved Density and Lower Capacitance

Transistor Fin Improvement

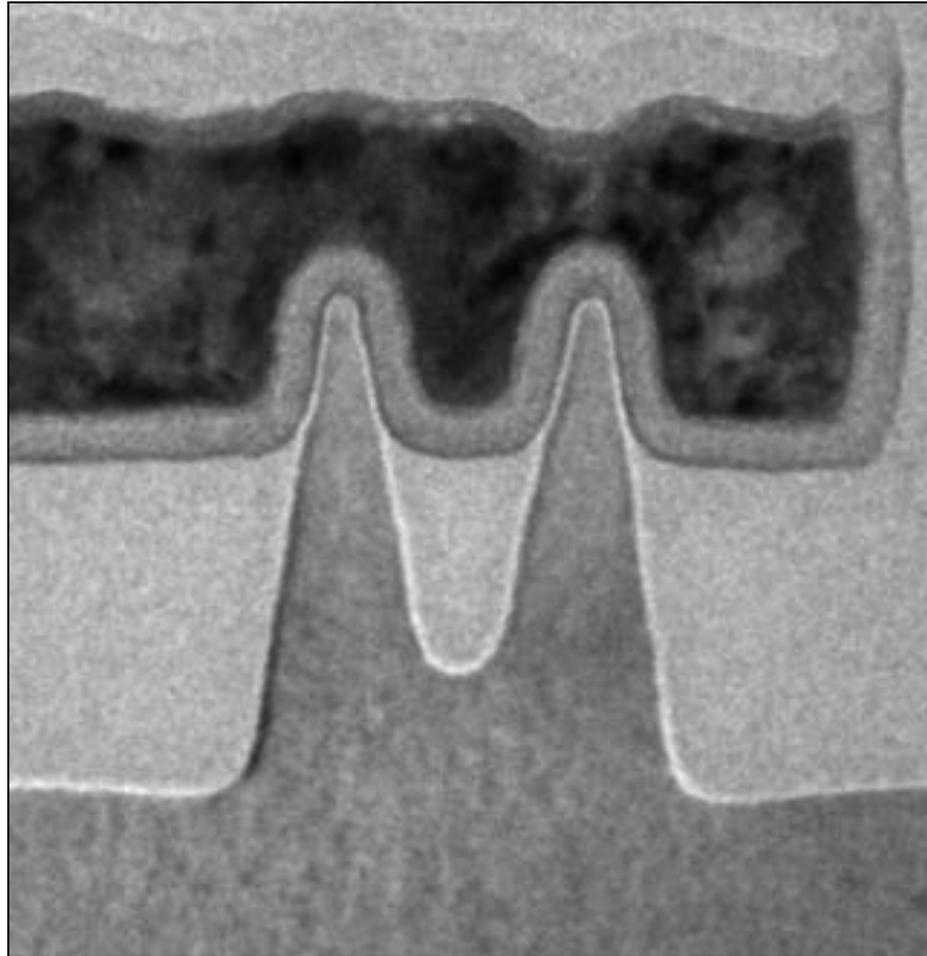


22 nm 1st Generation
Tri-gate Transistor

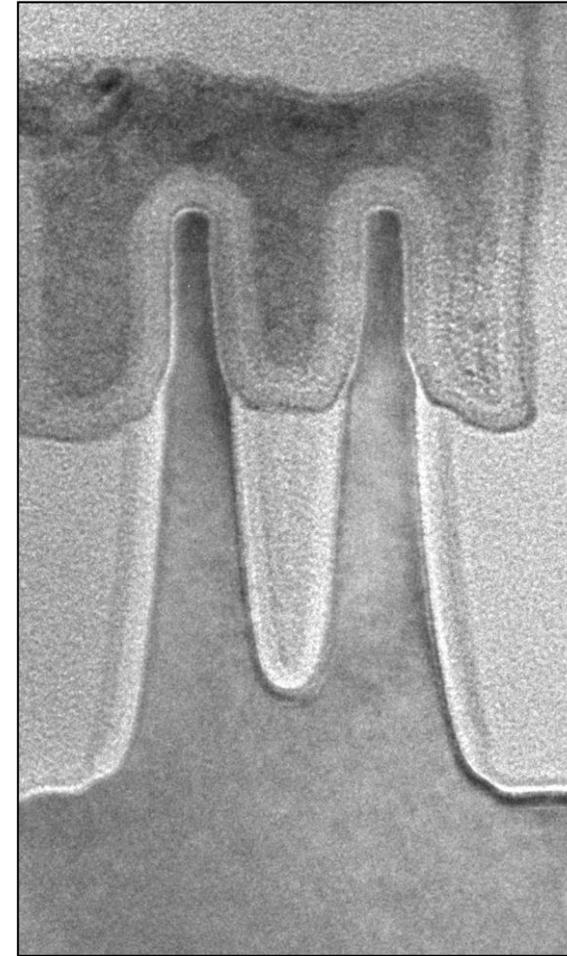


14 nm 2nd Generation
Tri-gate Transistor

Transistor Fin Improvement



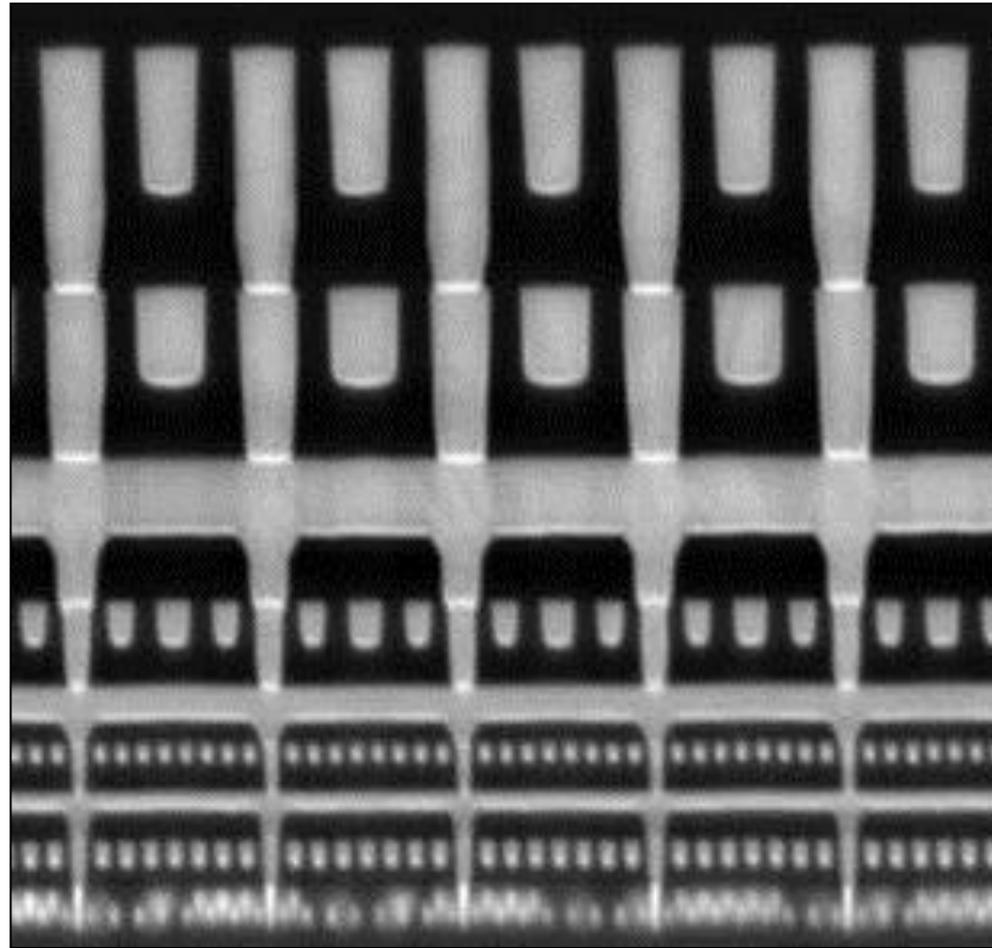
22 nm 1st Generation
Tri-gate Transistor



14 nm 2nd Generation
Tri-gate Transistor

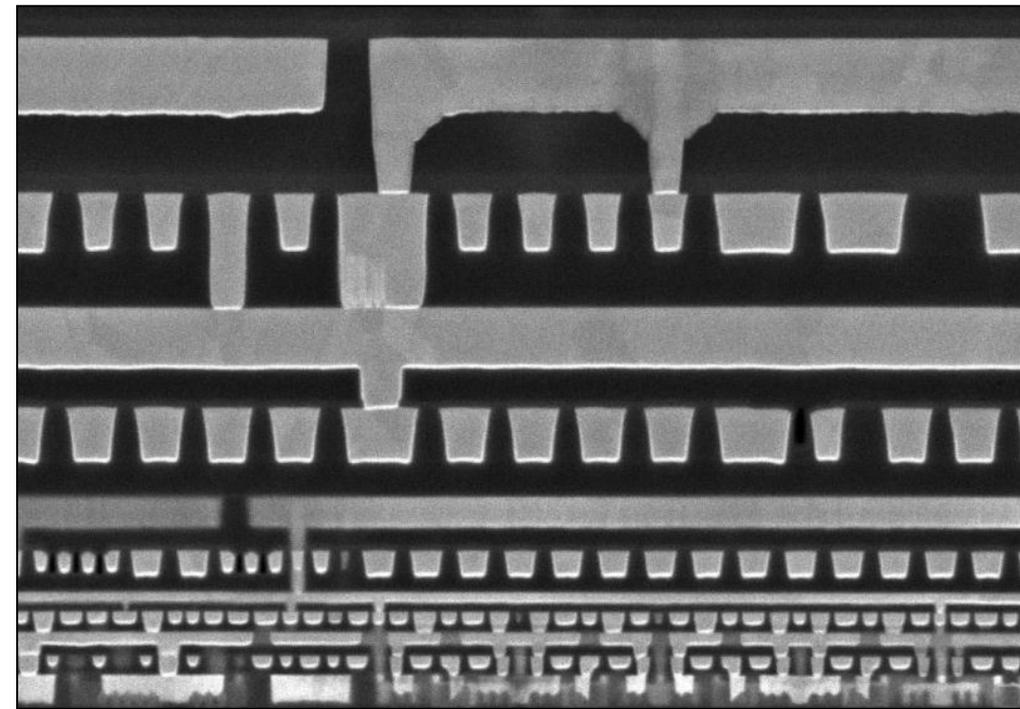
Interconnects

22 nm Process



80 nm minimum pitch

14 nm Process

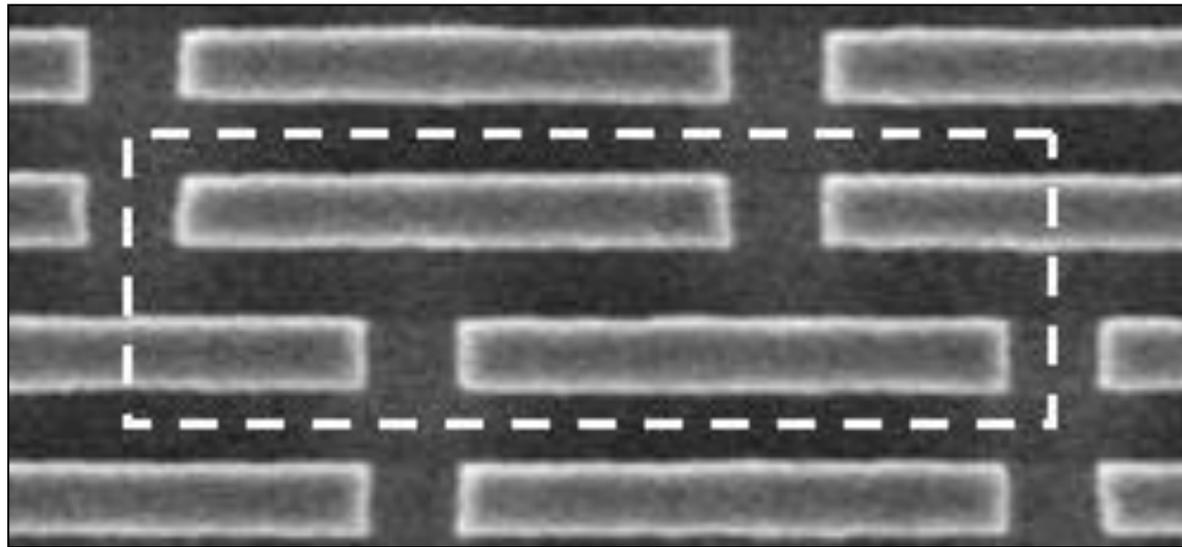


52 nm (0.65x) minimum pitch

*52 nm Interconnect Pitch Provides
Better-than-normal Interconnect Scaling*

SRAM Memory Cells

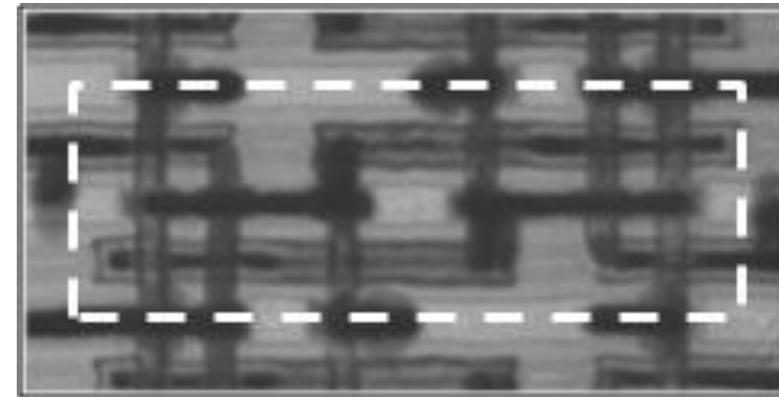
22 nm Process



.108 μm^2

(Used on CPU products)

14 nm Process

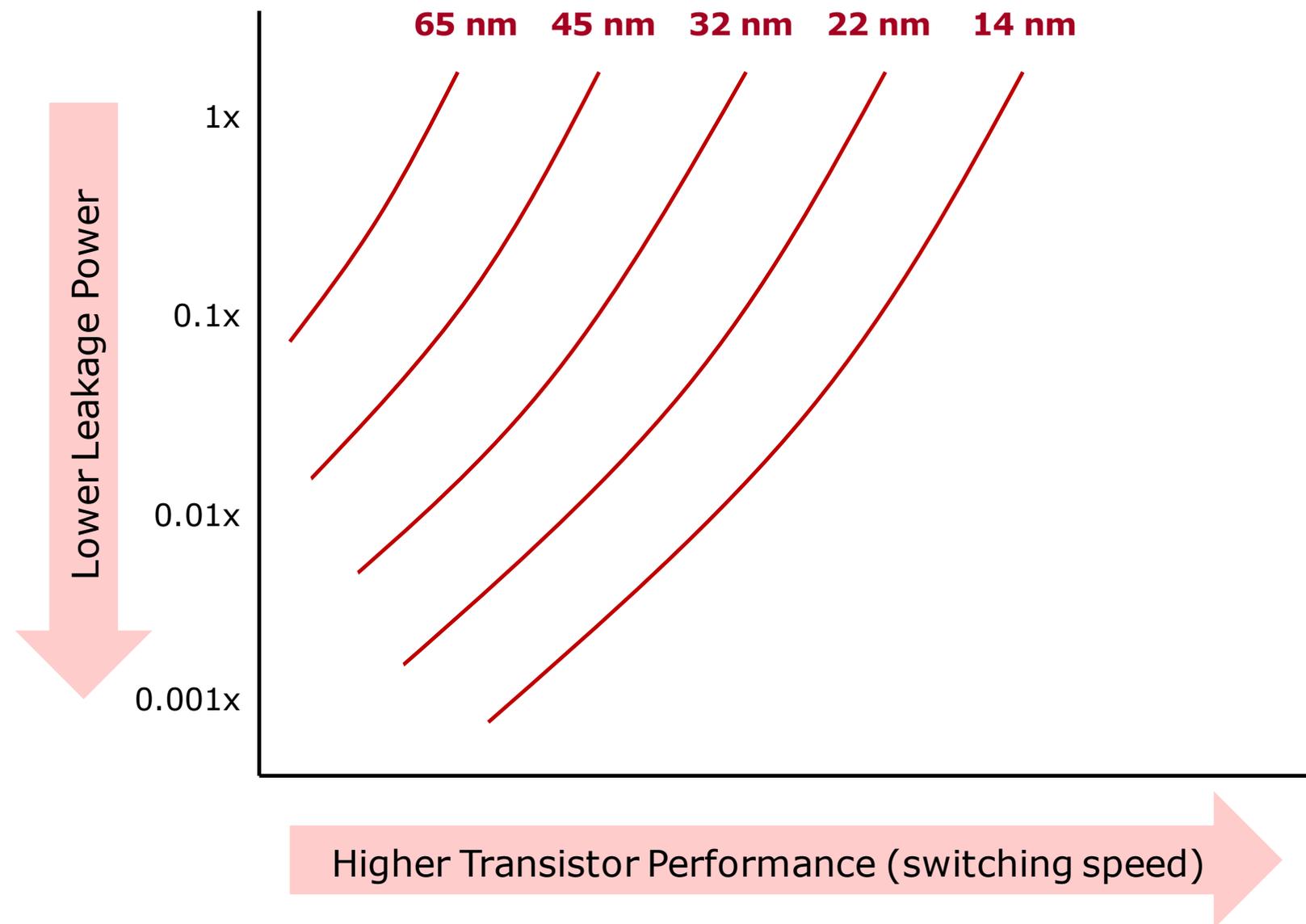


.0588 μm^2

(0.54x area scaling)

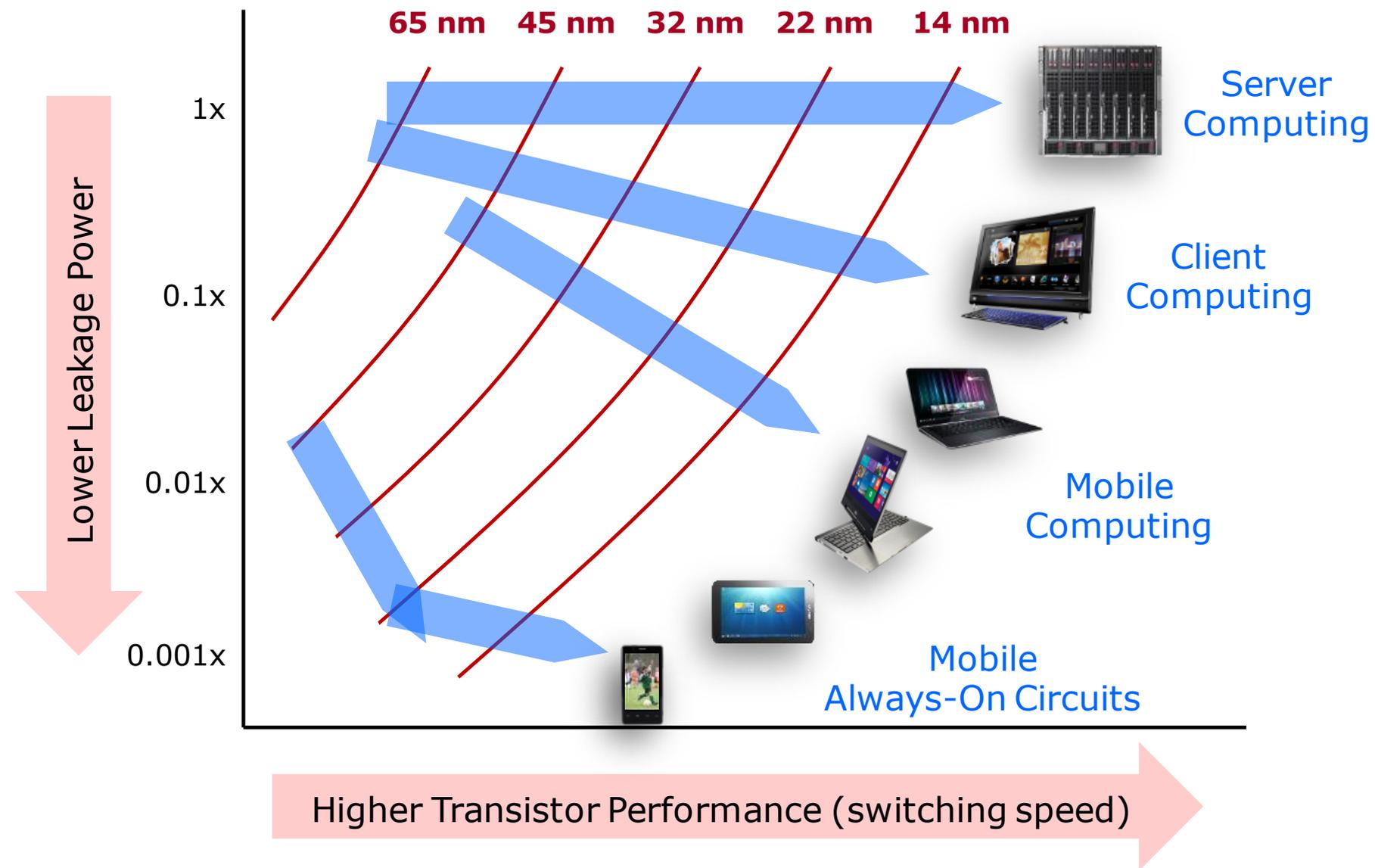
14 nm Design Rules + 2nd Generation Tri-gate Transistor Provides Industry-leading SRAM Density

Transistor Performance vs. Leakage



14 nm Transistors Provide Improved Performance and Leakage ...

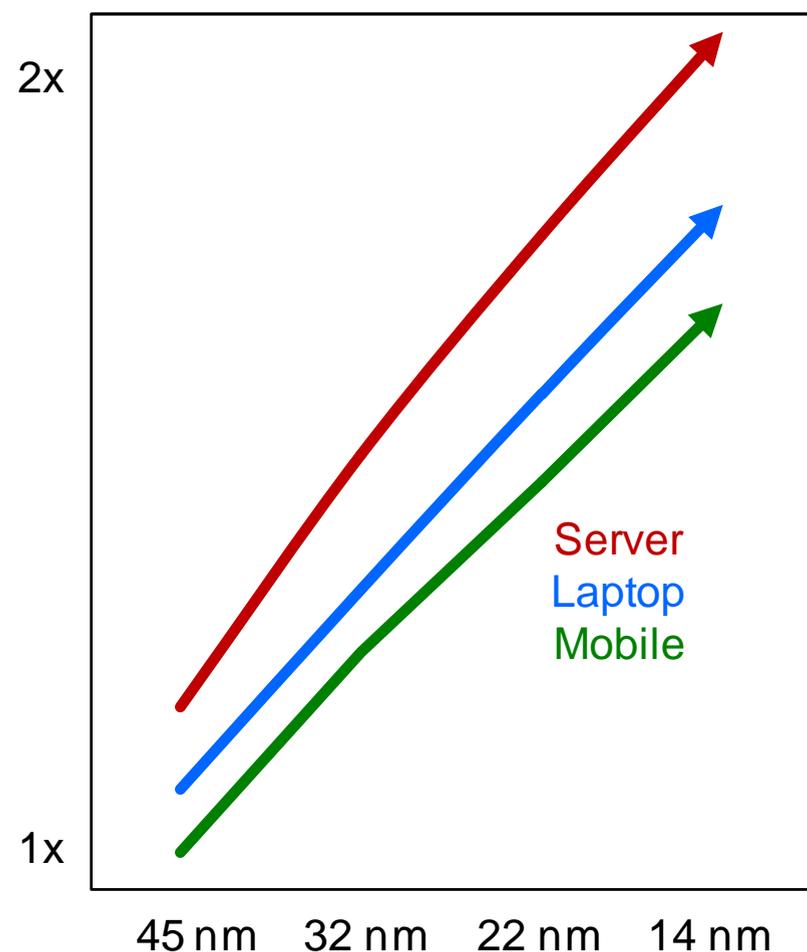
Transistor Performance vs. Leakage



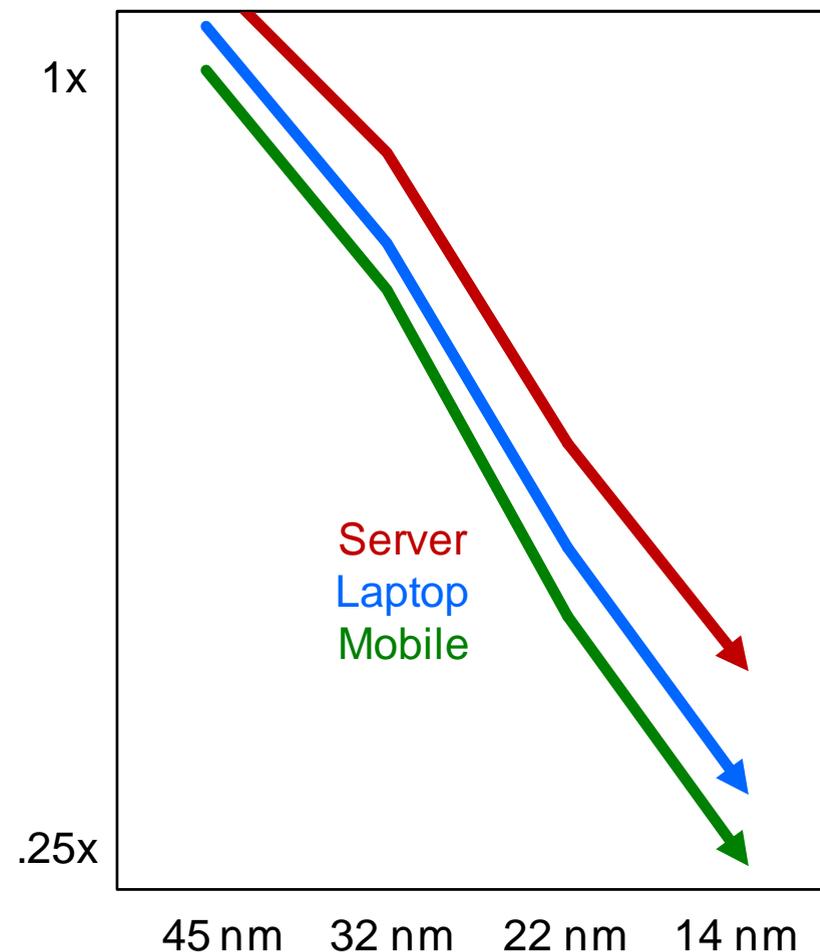
... To Support a Wide Range of Products

Product Benefits

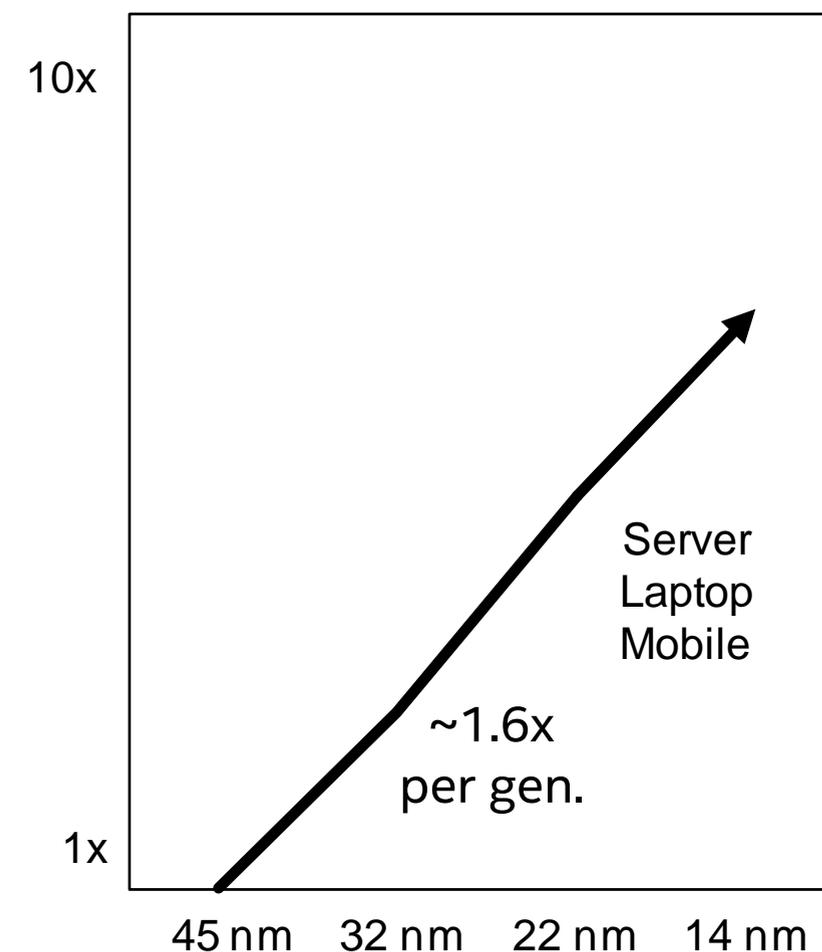
Performance



Active Power (Includes performance increase)



Performance per Watt



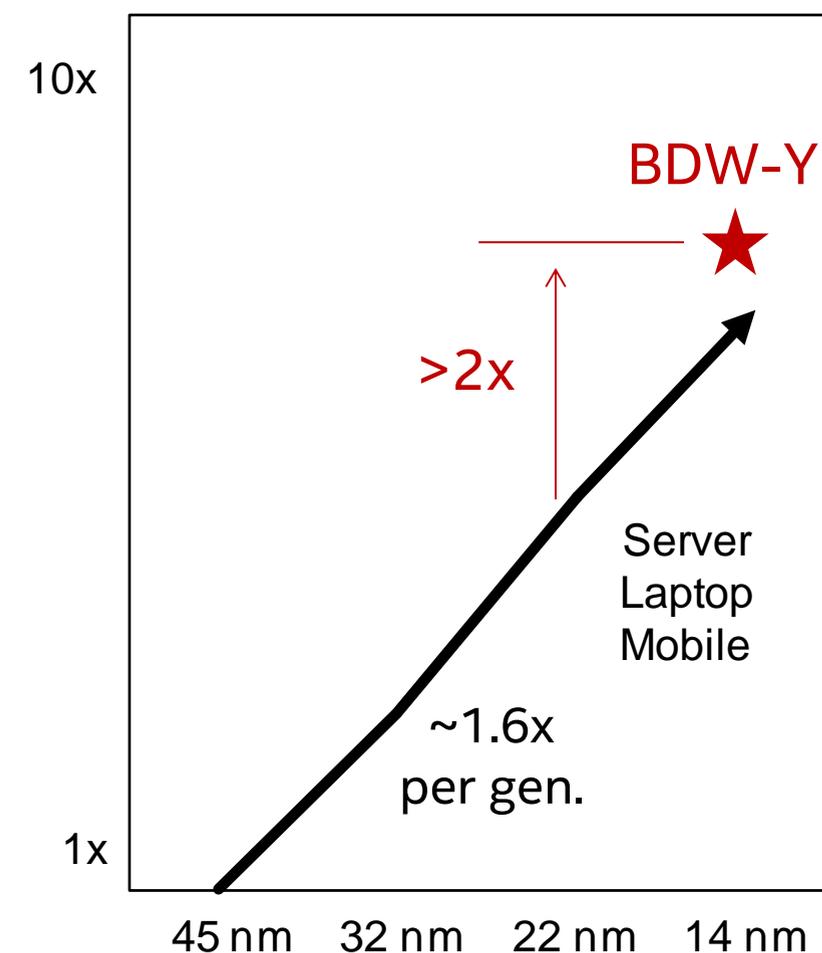
New technology generations provide improved performance and/or reduced power, but the key benefit is improved performance per watt

Product Benefits

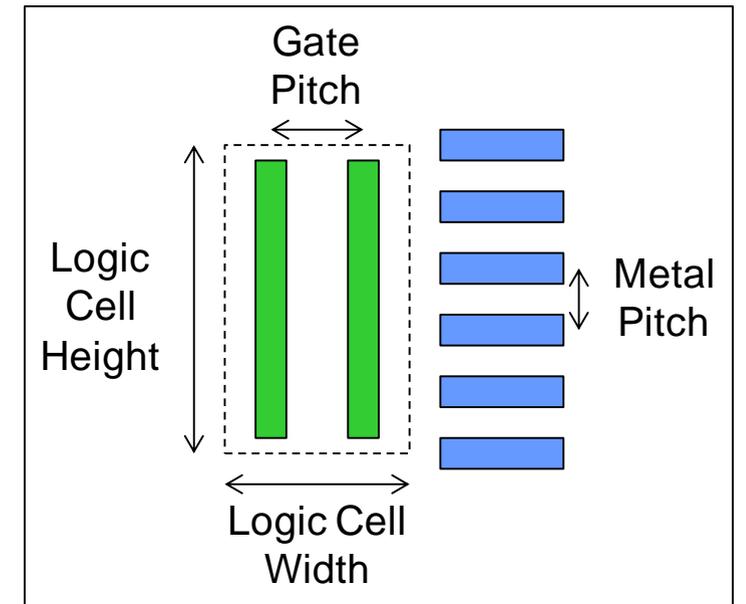
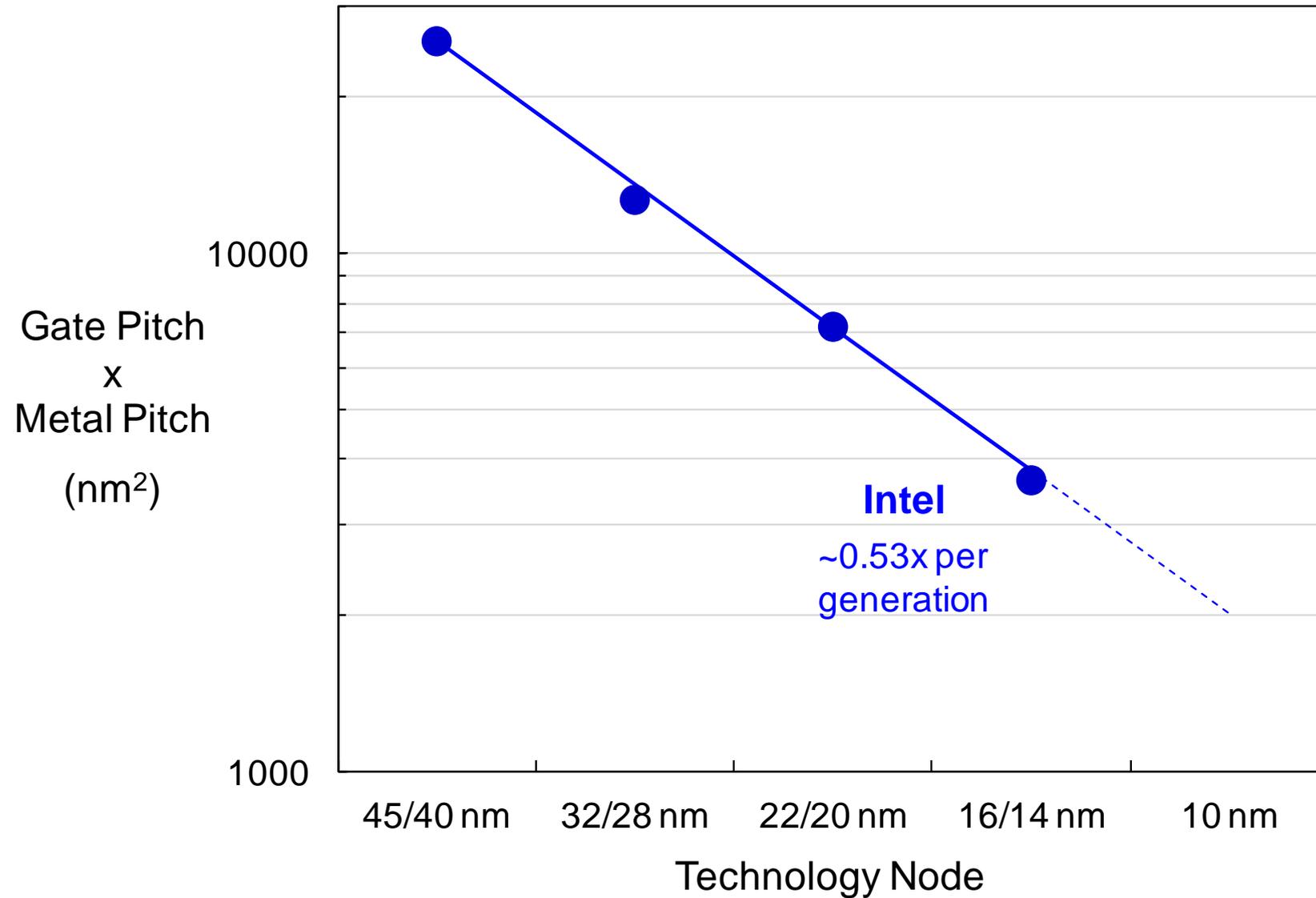
14 nm BDW-Y delivers >2x improvement in performance per watt

- 2nd generation Tri-gate transistors with improved low voltage performance and lower leakage
- Better than normal area scaling
- Extensive design-process co-optimization
- Micro-architecture optimizations for Cdyn reduction

Performance per Watt

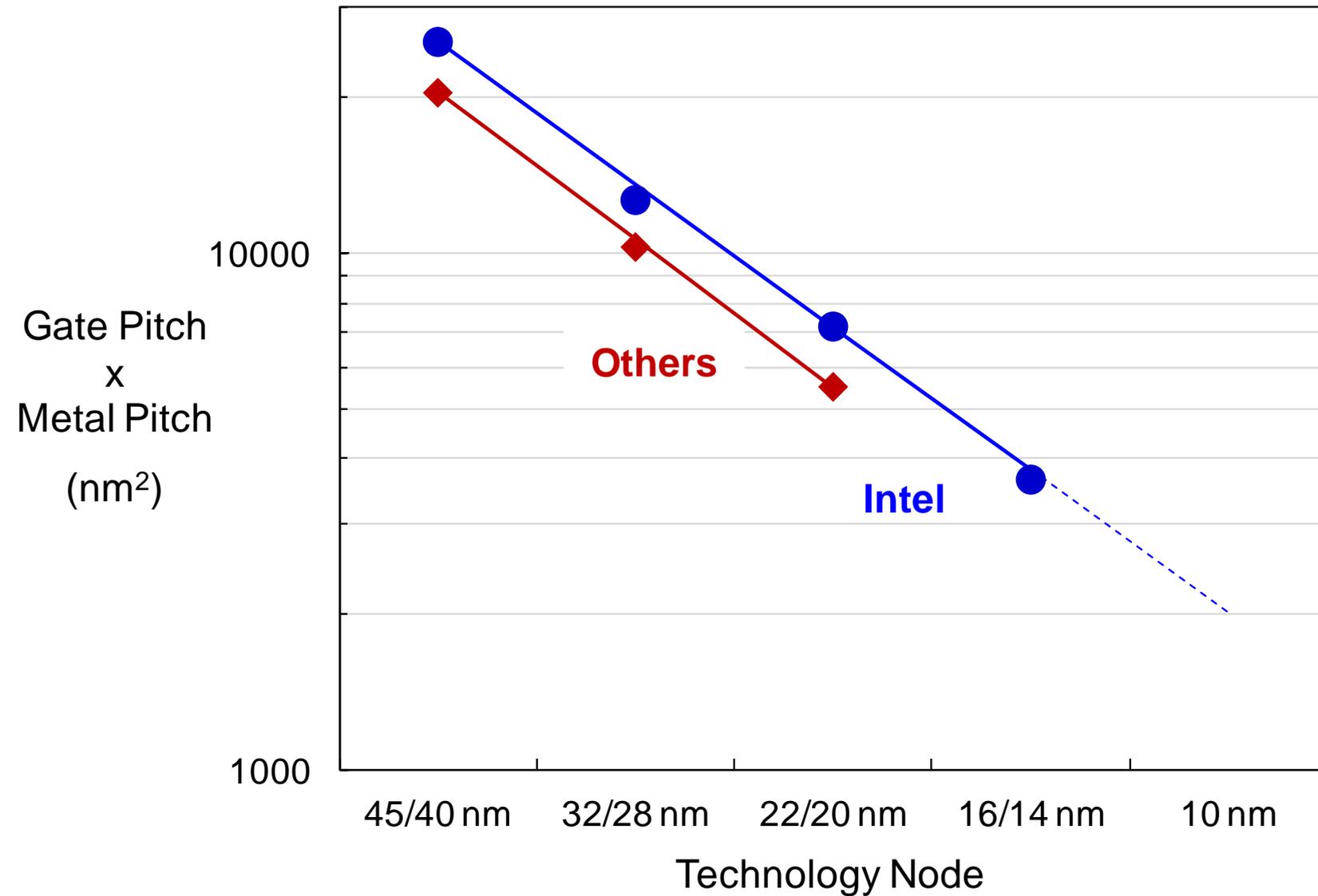


Logic Area Scaling



Logic area continues to scale ~0.53x per generation

Logic Area Scaling

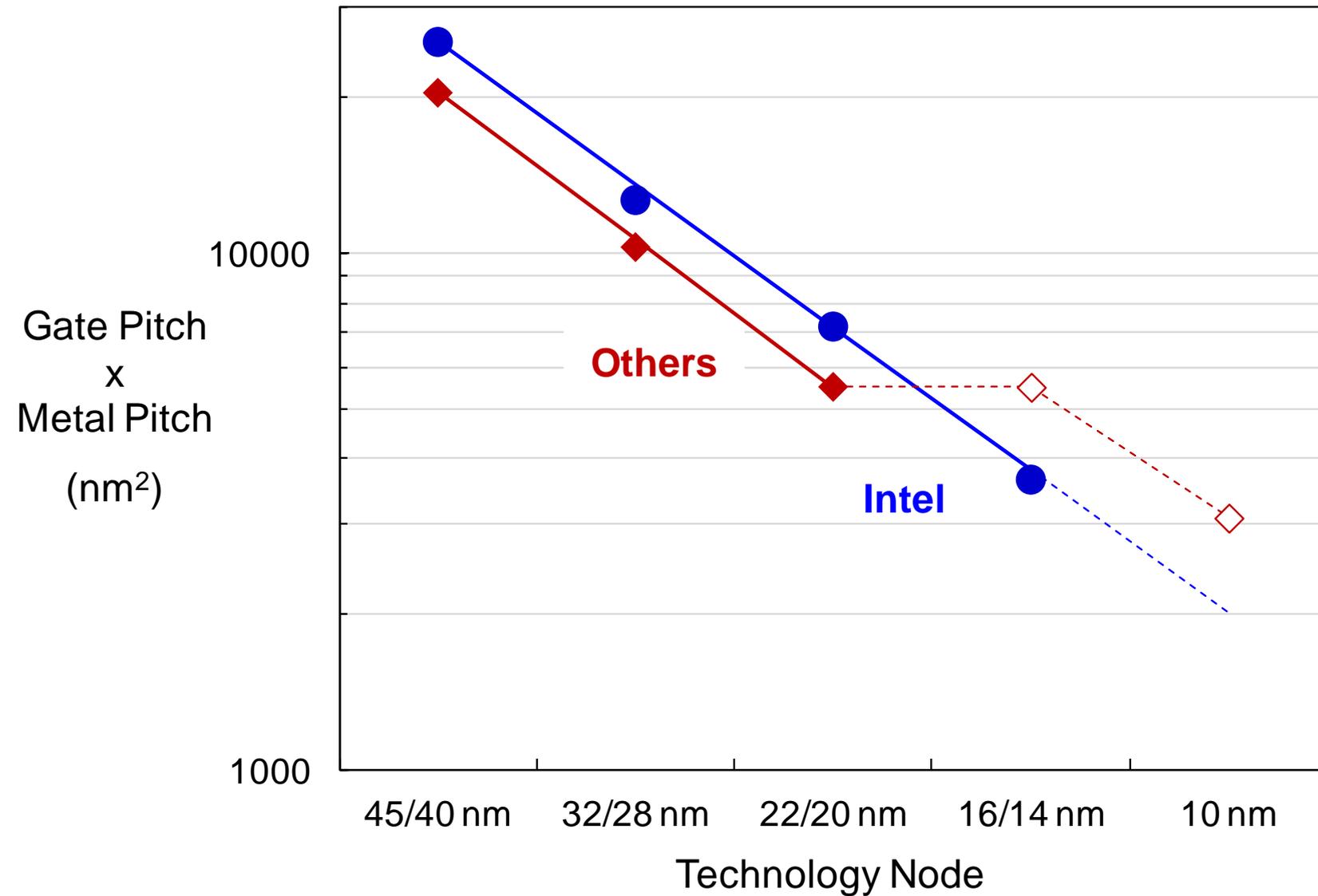


Others based on published information:

45nm: K-L Cheng (TSMC), 2007 IEDM, p. 243
28nm: F. Arnaud (IBM alliance), 2009 IEDM, p. 651
20nm: H. Shang (IBM alliance), 2012 VLSI, p. 129

In the Past, Others Tended to Have Better Density, but Came Later Than Intel

Logic Area Scaling

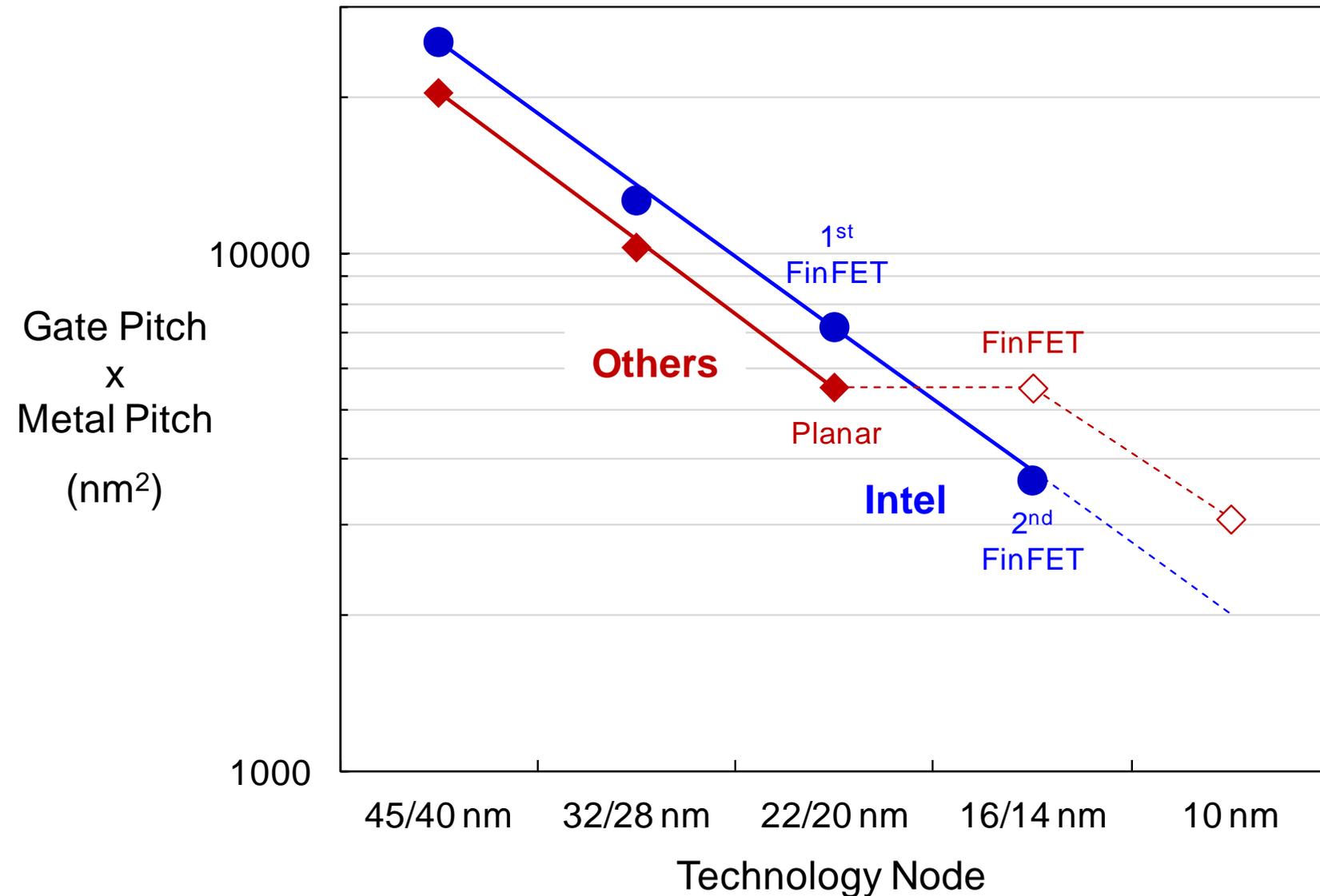


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- 16nm: S. Wu (TSMC), 2013 IEDM, p. 224
- 10nm: K-I Seo (IBM alliance), 2014 VLSI, p. 14

*Intel Continues Scaling at 14 nm While Others
Pause to Develop FinFETs*

Logic Area Scaling

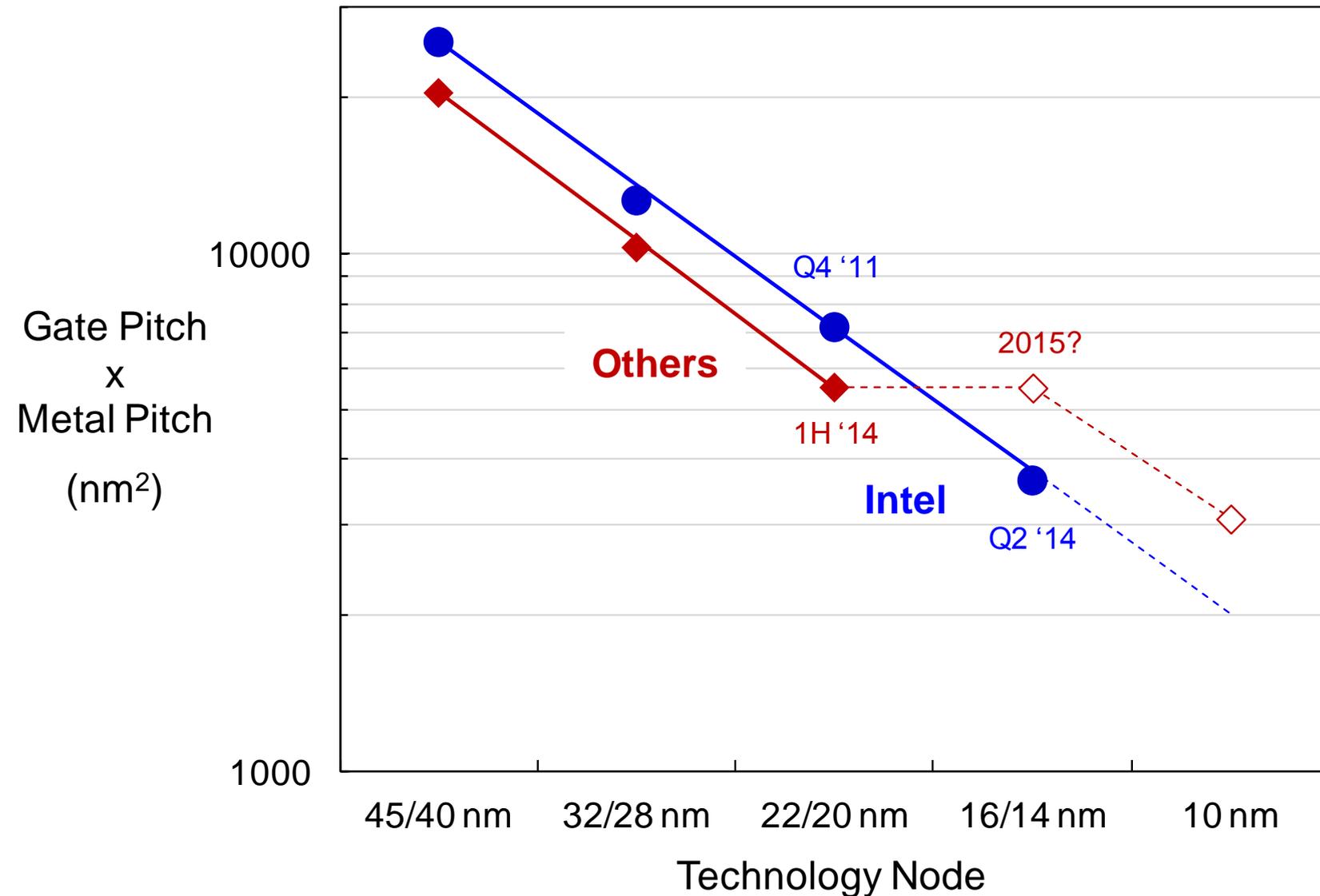


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Intel is Shipping its 2nd Generation FinFETs Before Others Ship Their 1st Generation

Logic Area Scaling



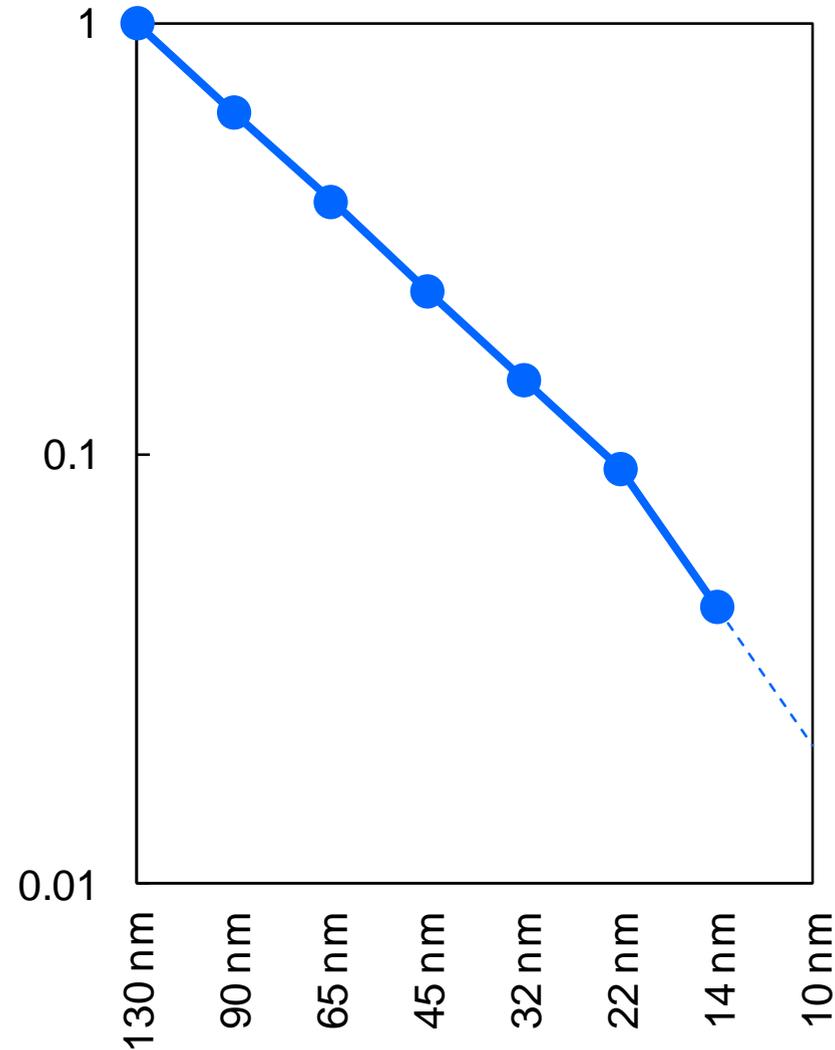
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*Intel has Developed a True 14 nm Technology
Denser and Earlier Than What Others Call "16 nm" or "14 nm"*

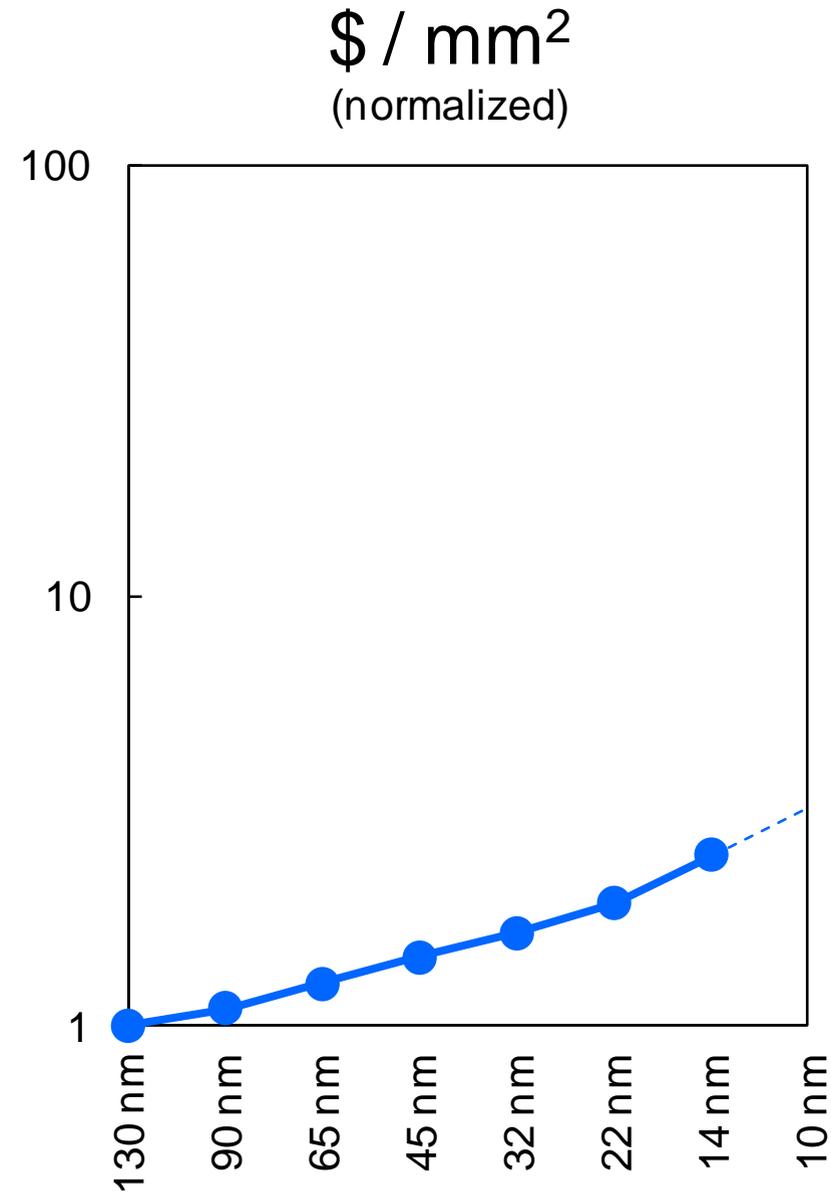
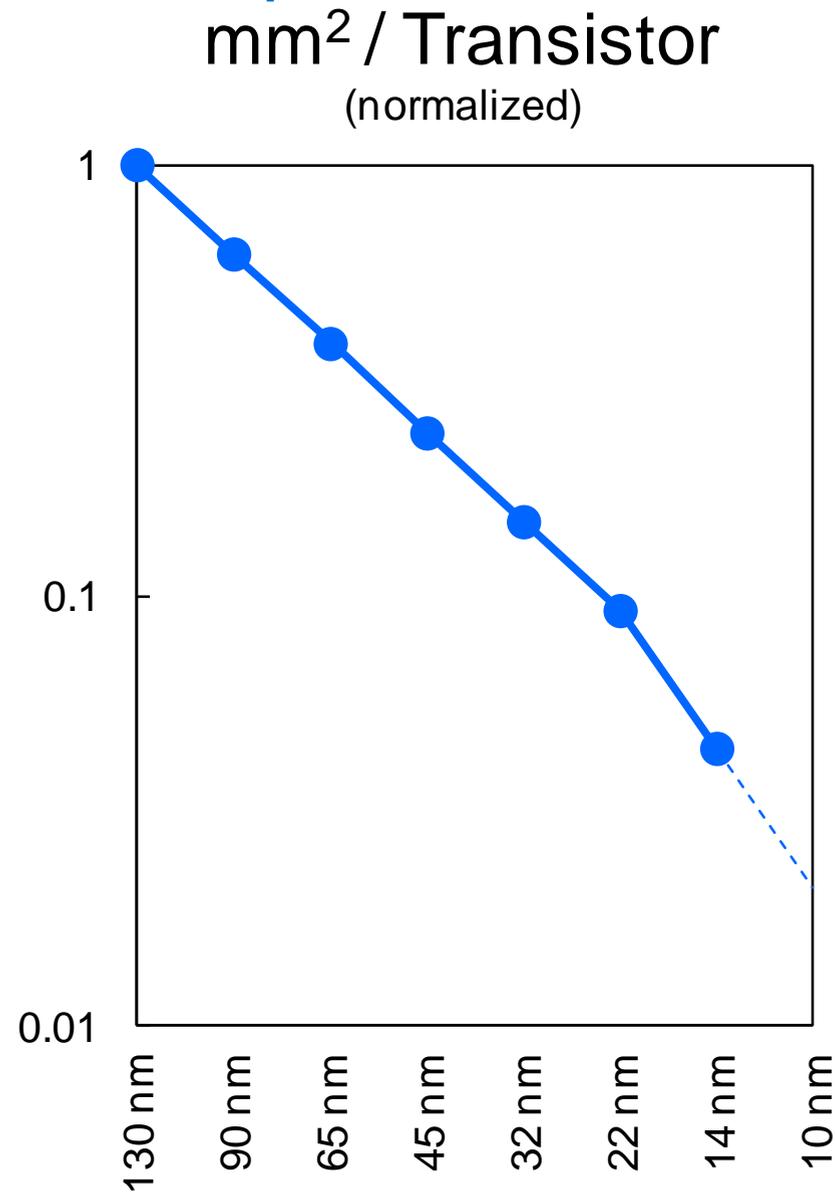
Cost per Transistor

mm² / Transistor
(normalized)



14 nm Achieves Better-than-Normal Area Scaling with Use of Advanced Double Patterning Techniques

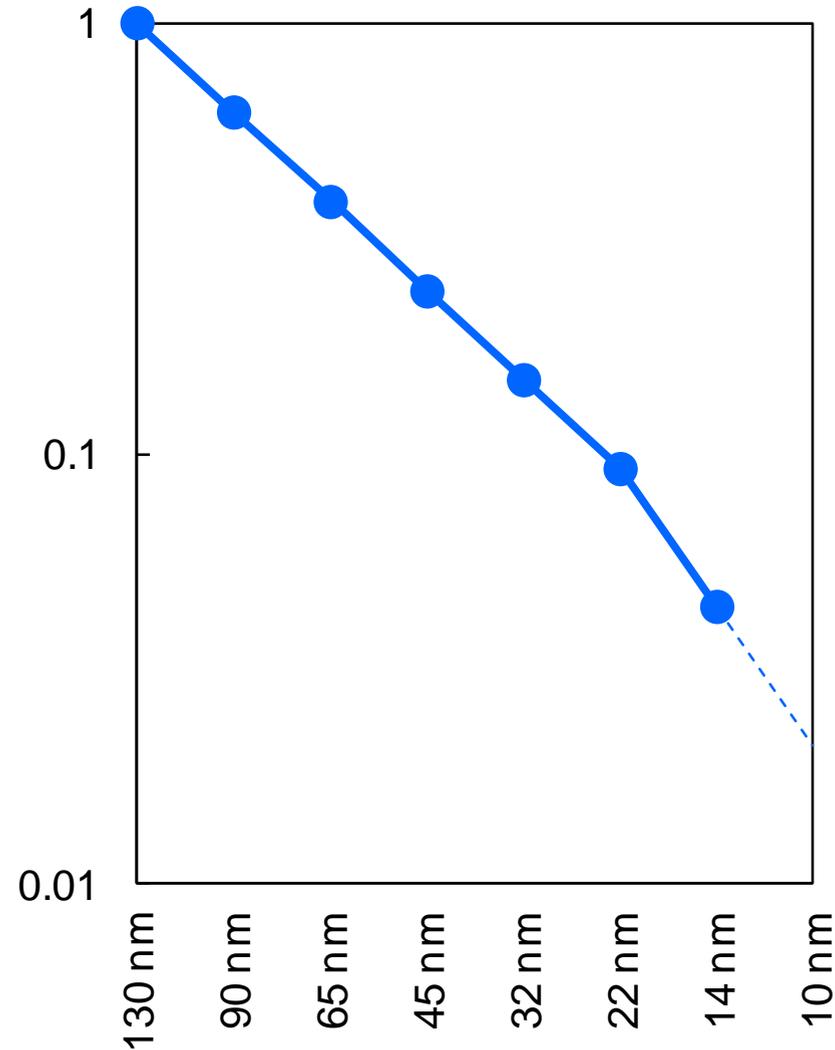
Cost per Transistor



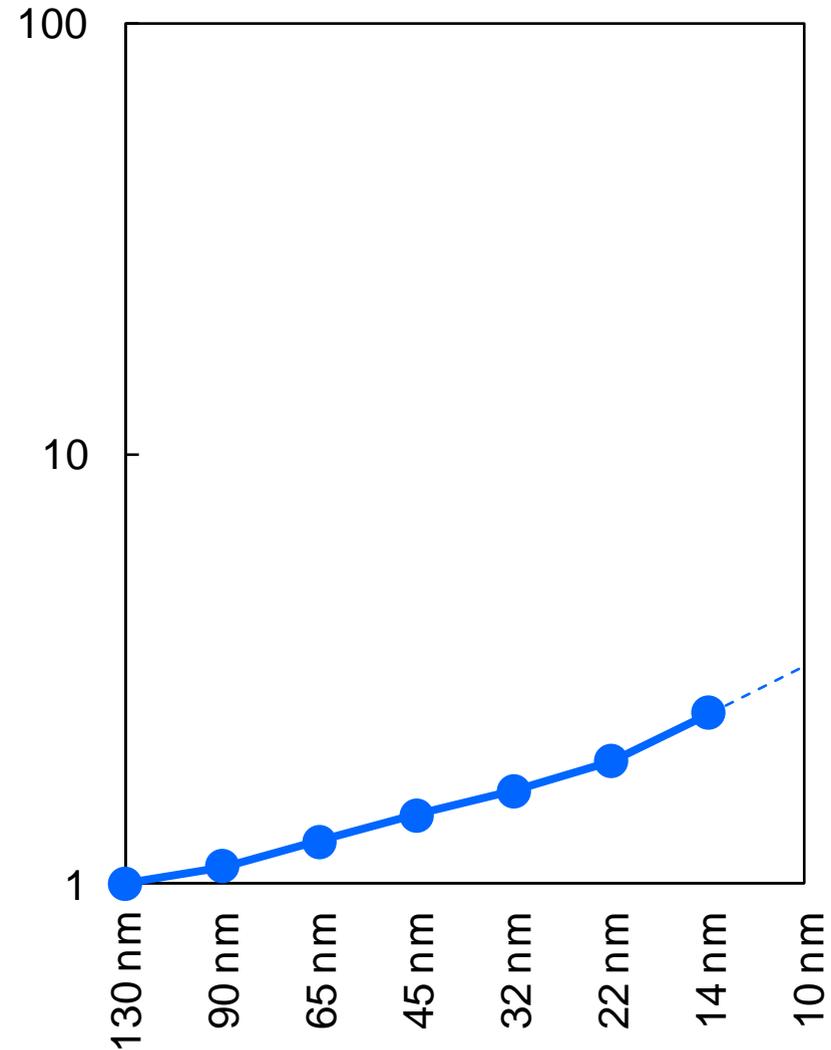
Wafer Cost Increasing Due to Added Masking Steps

Cost per Transistor

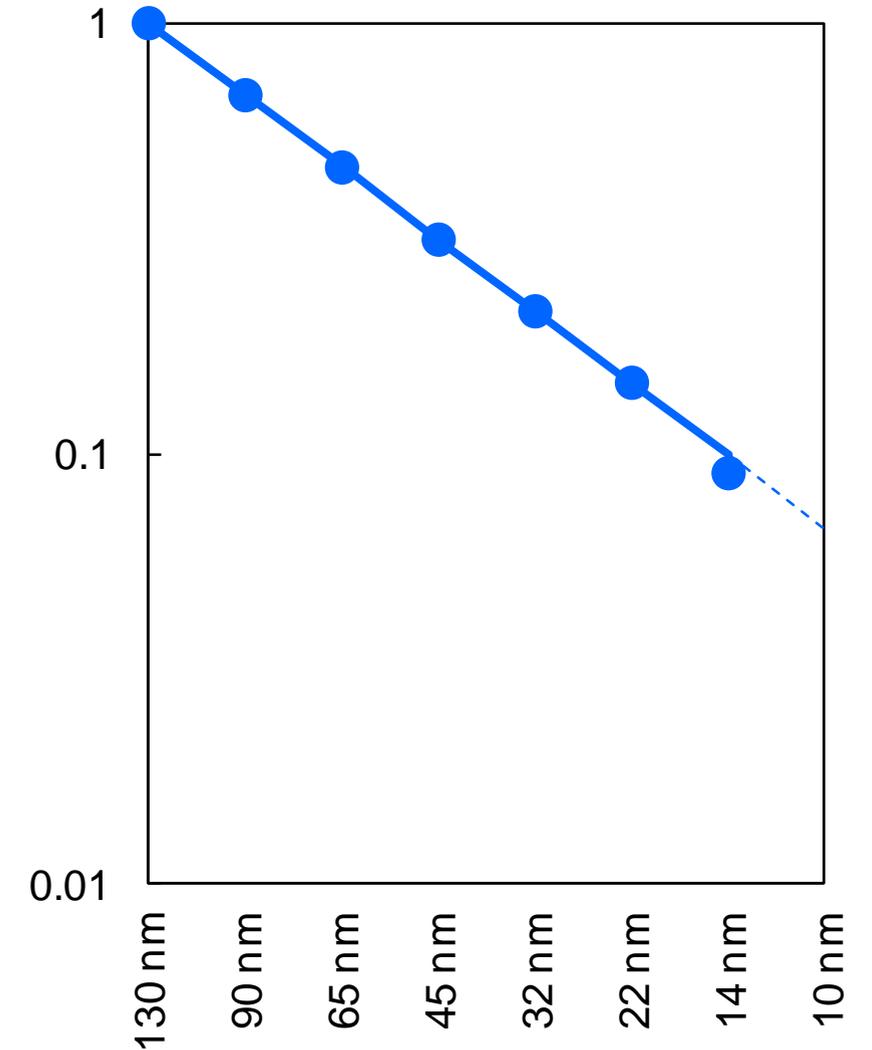
mm² / Transistor
(normalized)



\$ / mm²
(normalized)

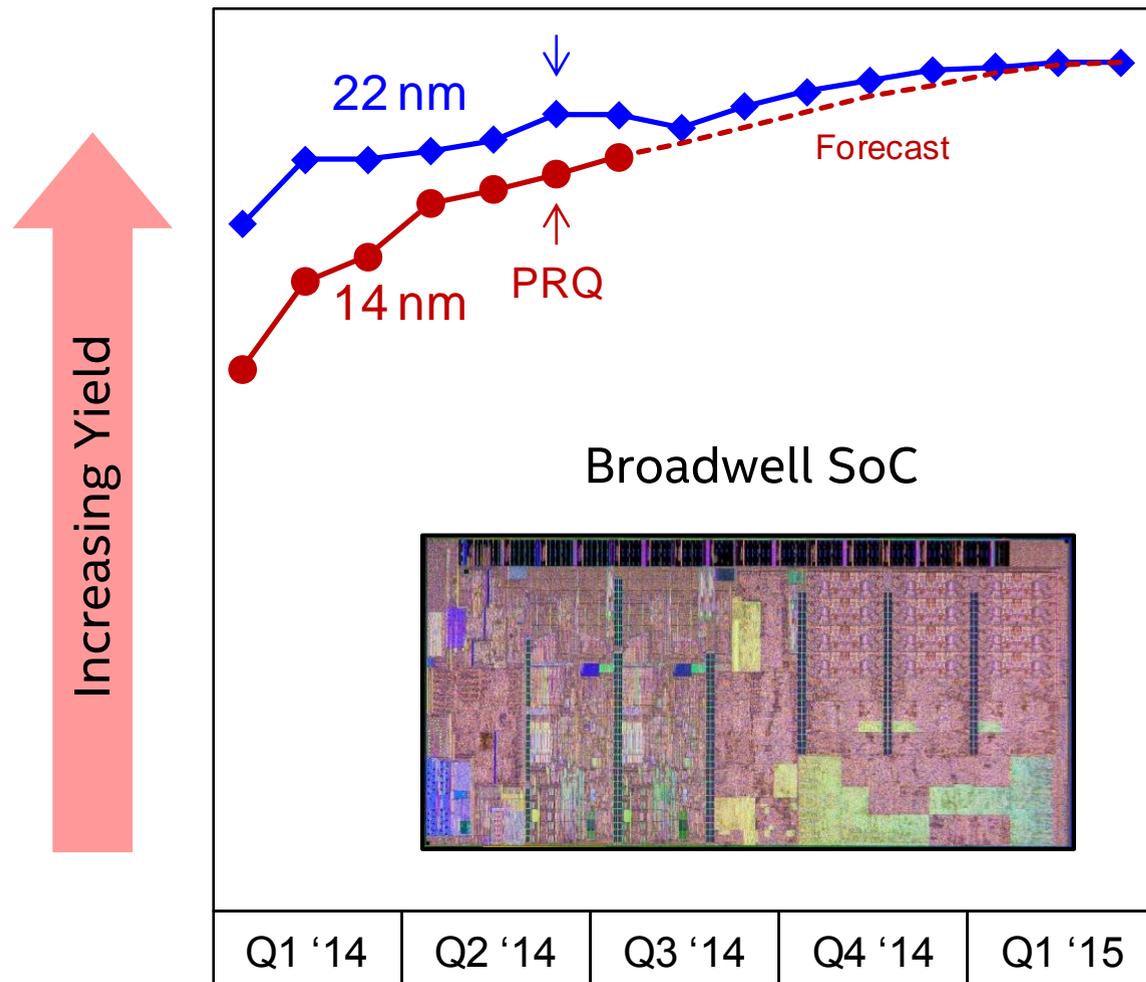


\$ / Transistor
(normalized)



Intel 14 nm Continues to Deliver Lower Cost per Transistor

14 nm Broadwell SoC Yield Trend



- 14 nm product yield is now in healthy range with further improvements coming
- Process and lead product are qualified and in volume production
- 14 nm manufacturing fabs are located in Oregon (2014), Arizona (2014) and Ireland (2015)
- Production yield and wafer volume are projected to meet the needs of multiple 14 nm product ramps in 1H '15

22 nm data are shifted to align date of lead product qual
Depicts relative health, lines not to scale

*Leadership Technologies are Never Easy
(at First!)*

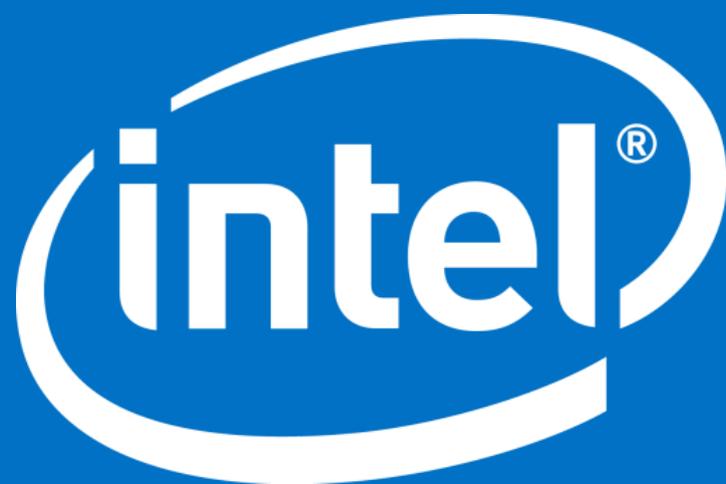
Summary

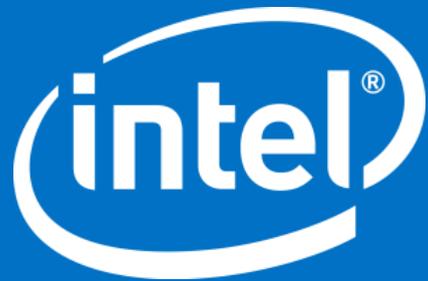
Intel has developed a true 14 nm technology with industry-leading performance, power, density and cost per transistor

- 2nd generation Tri-gate transistors
- 42 nm fin pitch
- 70 nm gate pitch
- 52 nm interconnect pitch
- .0588 μm^2 SRAM cell

Intel's 14 nm technology will be used to manufacture a wide range of products, from high performance to low power

The 14 nm technology and the lead Broadwell SoC product are now qualified and in volume production





Broadwell Microarchitecture Disclosures

Stephan Jourdan

Intel Fellow

Director, System-on-Chip Architecture

Platform Engineering Group

August 11, 2014

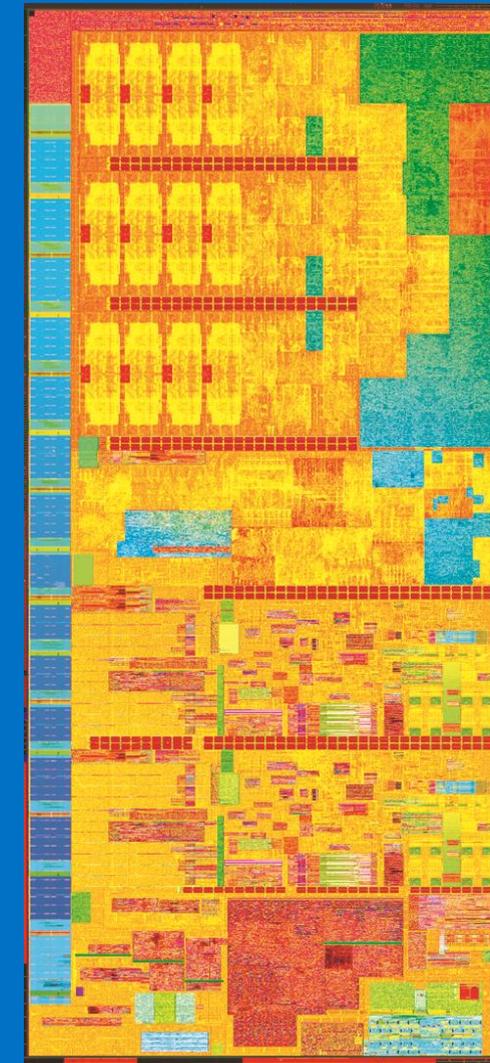
Agenda: Broadwell Micro-architecture

The Fanless Challenge

The Journey to Fanless

Broadwell Converged Core Improvements

Graphics/Media/Display

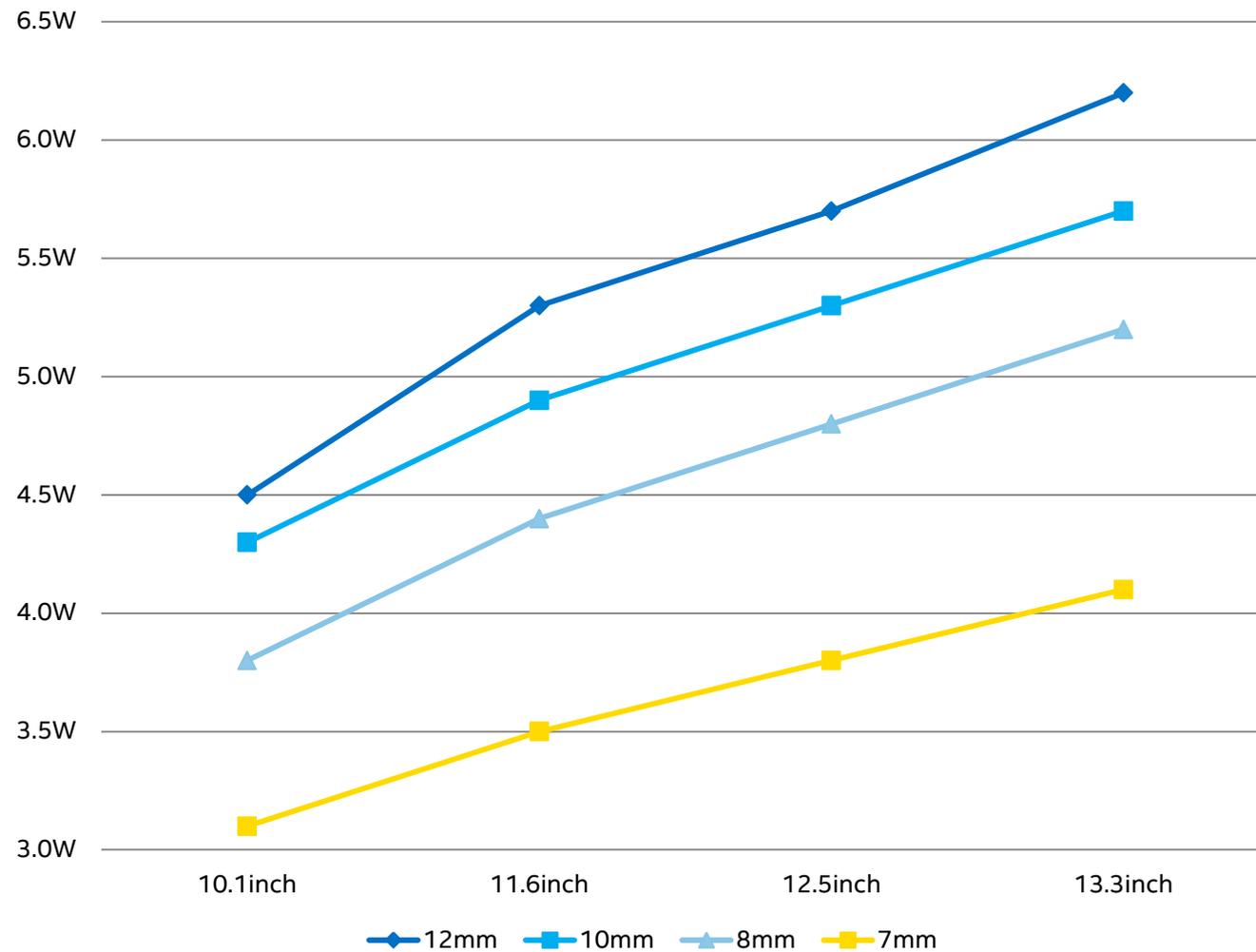


Delivering the Intel® Core™ Processor Experience in Fanless Form Factors

- Performance, Responsiveness, Battery Life, Ecosystem, etc.
- Embraced Outside-In Approach

The Fanless Challenge:

8-10mm, 10.1" Display, Fanless Designs Allow 3-5W Operations



Metal chassis, 41C T_{skin} , 25C $T_{Ambient}$

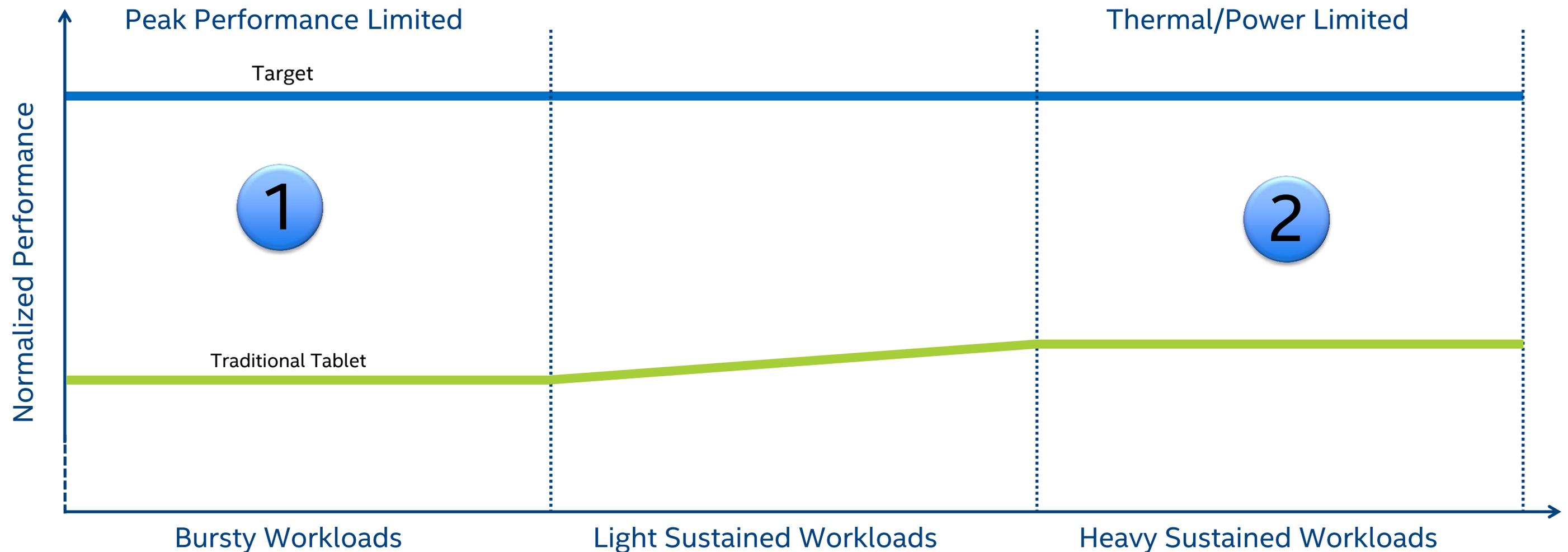
SoC Sustainable Power Depends on:

1. Display Size (X and Y dimensions)
2. Chassis Z-height
3. Chassis material and target skin temp
4. Ambient temp

The Fanless Challenge:

Delivering the Intel® Core™ Processor Experience in Fanless Form Factors

1. Maintaining Peak Burst Capability
2. Providing Power / Perf Efficiency



The Journey to Fanless:

- 14nm Process & Design Co-optimization
- Packaging and Form Factor Innovations
- 2nd Gen FIVR and 3DL Technology
- Enhanced Power Management
- Aggressive Power Reduction

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Broadwell Y 14nm Design/Process Optimizations Delivered 2x Lower Power than Traditional Scaling

A new process flavor for fanless optimization point for BDW –Y

	Traditional	14nm Broadwell Y Process Flavor	SoC Impact
Capacitance	0.75x	0.65x	25% lower power Enabled by transistor/interconnect scaling and optimizations
Lower Minimum operating Voltage	Same	10% lower	20% lower power Enabled by lower variation and design optimizations
Low Voltage Transistor Performance	Traditionally optimized for high voltage operation	10-15% transistor performance improvement	14nm was optimized for low-voltage performance
Leakage	0.8x	Optimized for 2X lower leakage	~10% lower power 14nm natively optimized for BDW-Y
Area scaling		0.51x (feature neutral) 0.63x (with features)	Enabled by 14nm design rule and density

The Journey to Fanless:

- 14nm Process & Design Co-optimization
- Packaging and Form Factor Innovations
- 2nd Gen FIVR and 3DL Technology
- Enhanced Power Management
- Aggressive Power Reduction

Broadwell Y Platform Enabled Board Area Reduction of ~25% Compared to Haswell

50% Smaller XY

30% Smaller Z

Key Enablers:

- 0.63x scaling due to 14nm
- 0.5mm ball pitch
- 200um PKG Core
- 170um thin die
- 3DL



HSW U/Y
40x24x1.5mm



BDW-Y
30x16.5x1.04mm

The Journey to Fanless:

- 14nm Process & Design Co-optimization
- Packaging and Form Factor Innovations
- 2nd Gen FIVR and 3DL Technology
- Enhanced Power Management
- Aggressive Power Reduction

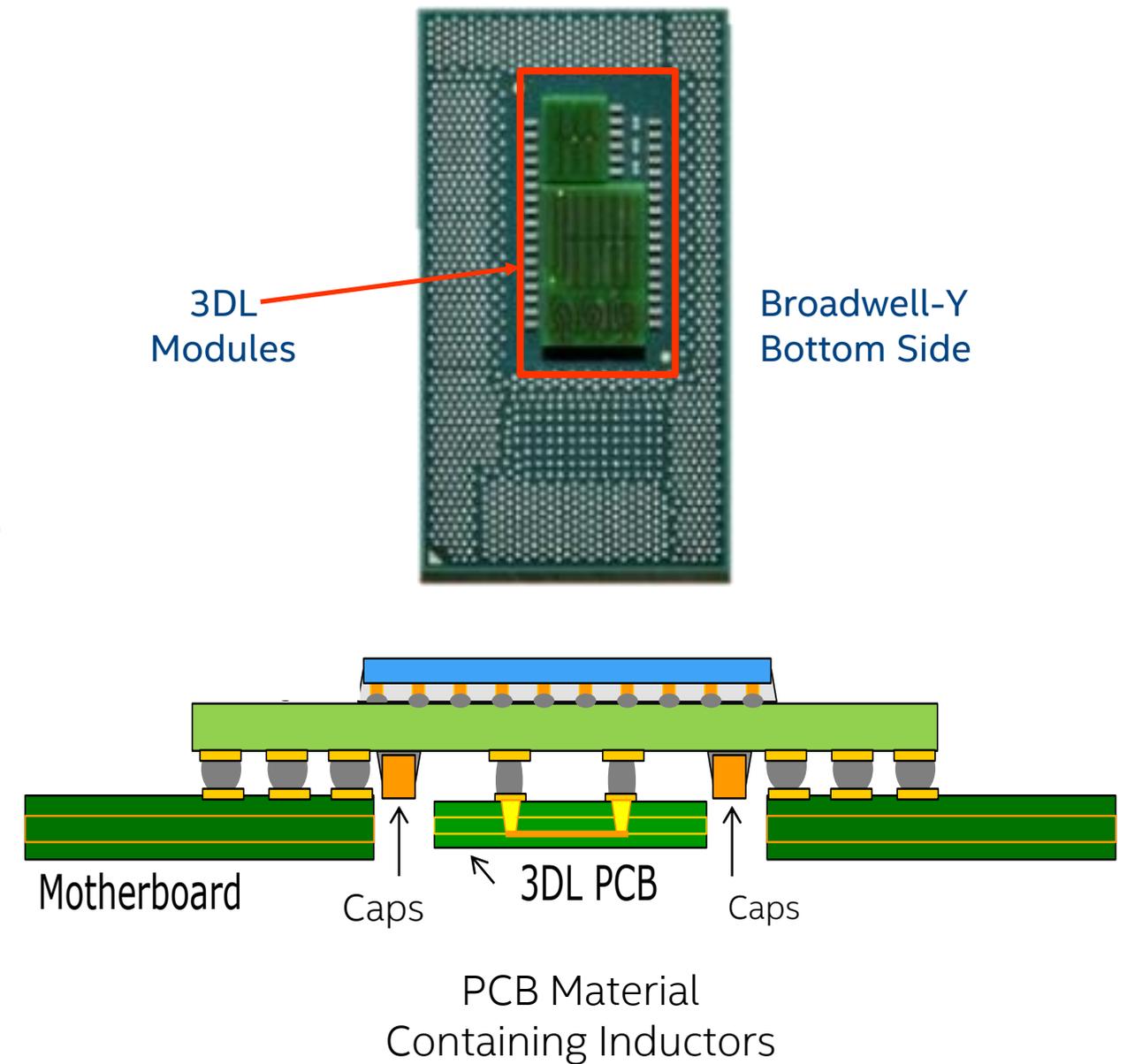
2nd Generation FIVR & 3DL Power Delivery Efficiency

2nd Gen of FIVR enables better efficiency at lower voltages:

- Non-linear Droop Control
- Dual FIVR LVR Mode

3DL Modules:

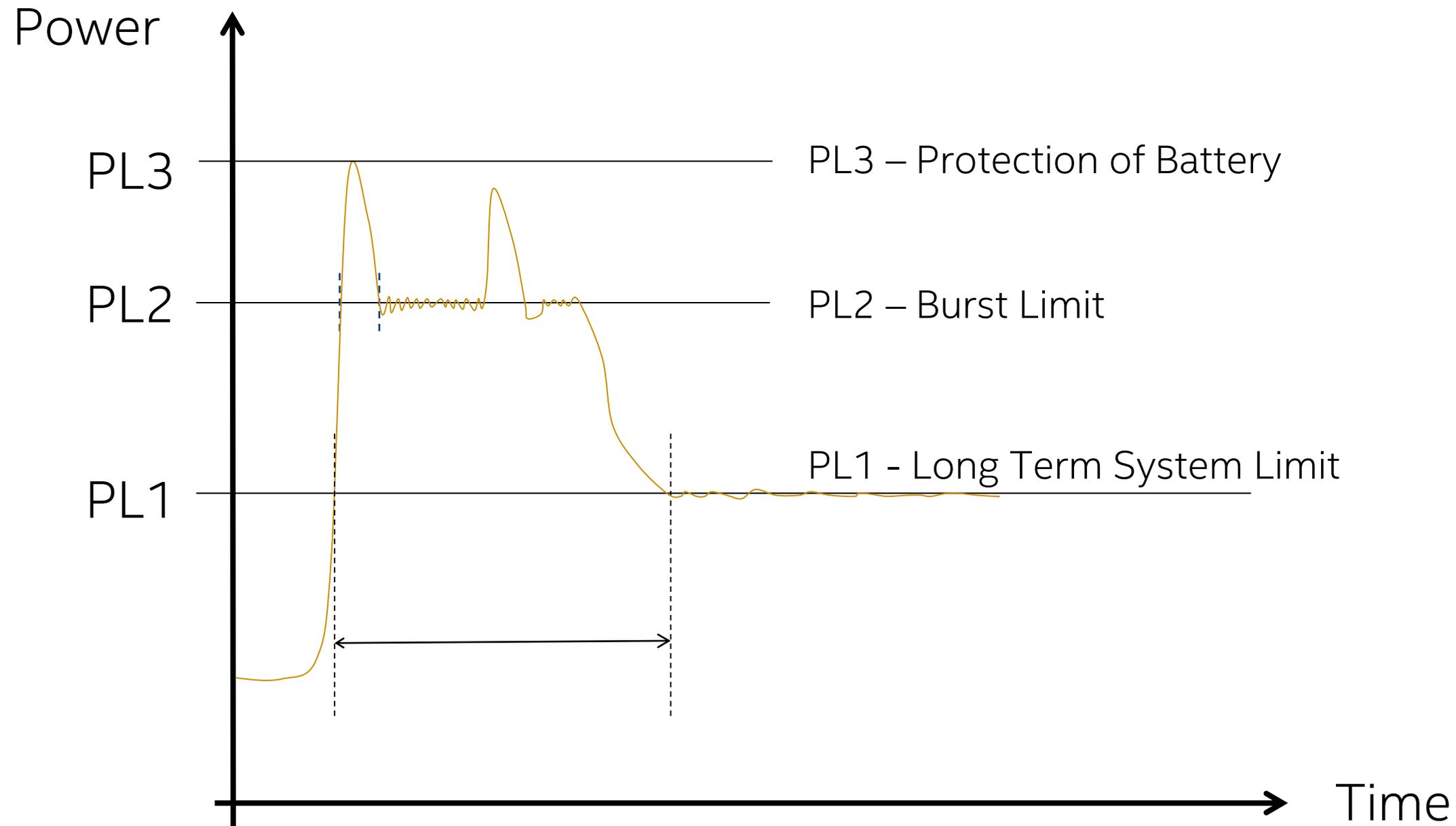
- Inductors removed from package substrate to modules under the die. Better efficiency and package Z-height reduction



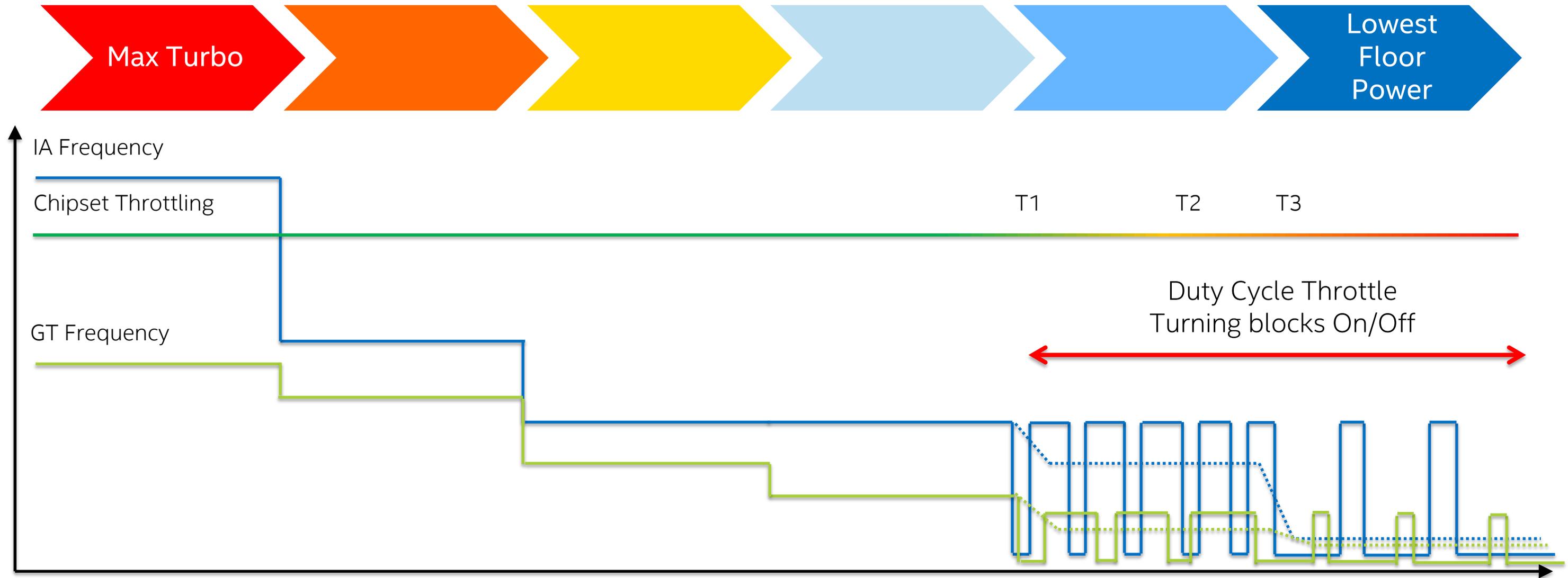
The Journey to Fanless:

- 14nm Process & Design Co-optimization
- Packaging and Form Factor Innovations
- 2nd Gen FIVR and 3DL Technology
- Enhanced Power Management
- Aggressive Power Reduction

Enhanced Turbo Boost: Maximizing the Opportunity to Boost While Maintaining System Reliability

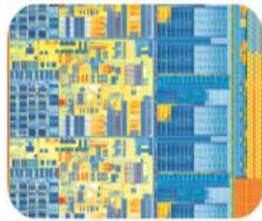


Managing Excursions



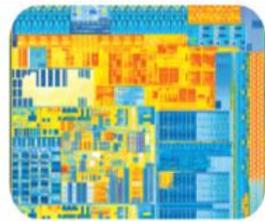
System Optimized Thermal Management: Platform Power Sharing for Optimal Performance

Intel Dynamic Power & Thermal Management Framework



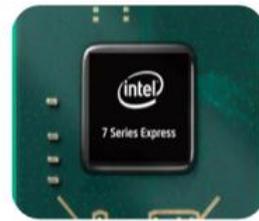
Processor

- Temperature
- Power Control
- P/T States



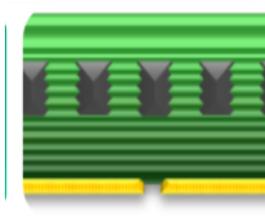
Processor Graphics

- Temperature
- Power Control
- RP States, EU^



PCH

- Temperature
- Power Control*



Memory

- Temperature
- Power Control



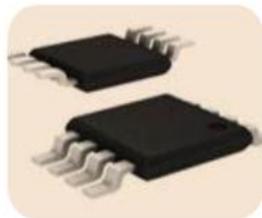
WLAN, WWAN

- Temperature
- Power Control*



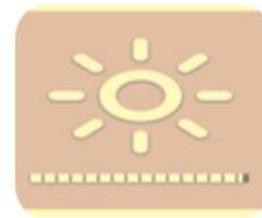
Battery Charger

- Charge Rate Control



Skin Thermal Sensor(s)

- Temperature



Display

- Brightness Control



System Fan(s)

- Fine Grained Fan Control

The Journey to Fanless:

- 14nm Process & Design Co-optimization
- Packaging and Form Factor Innovations
- 2nd Gen FIVR and 3DL Technology
- Enhanced Power Management
- Aggressive Power Reduction

SoC Power Reduction

$$\text{Power} = \text{Active Power } (C_{\text{dyn}} V^2 F) + \text{Leakage Power}$$

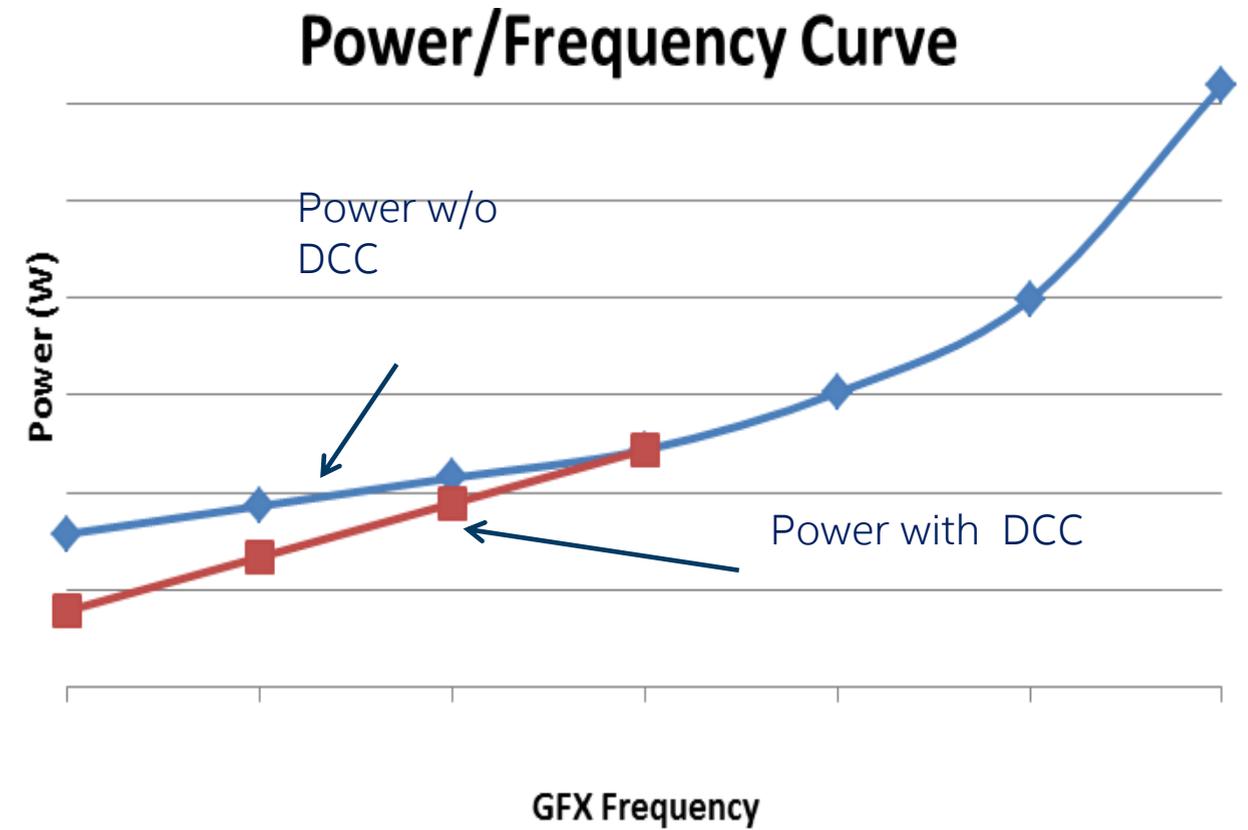
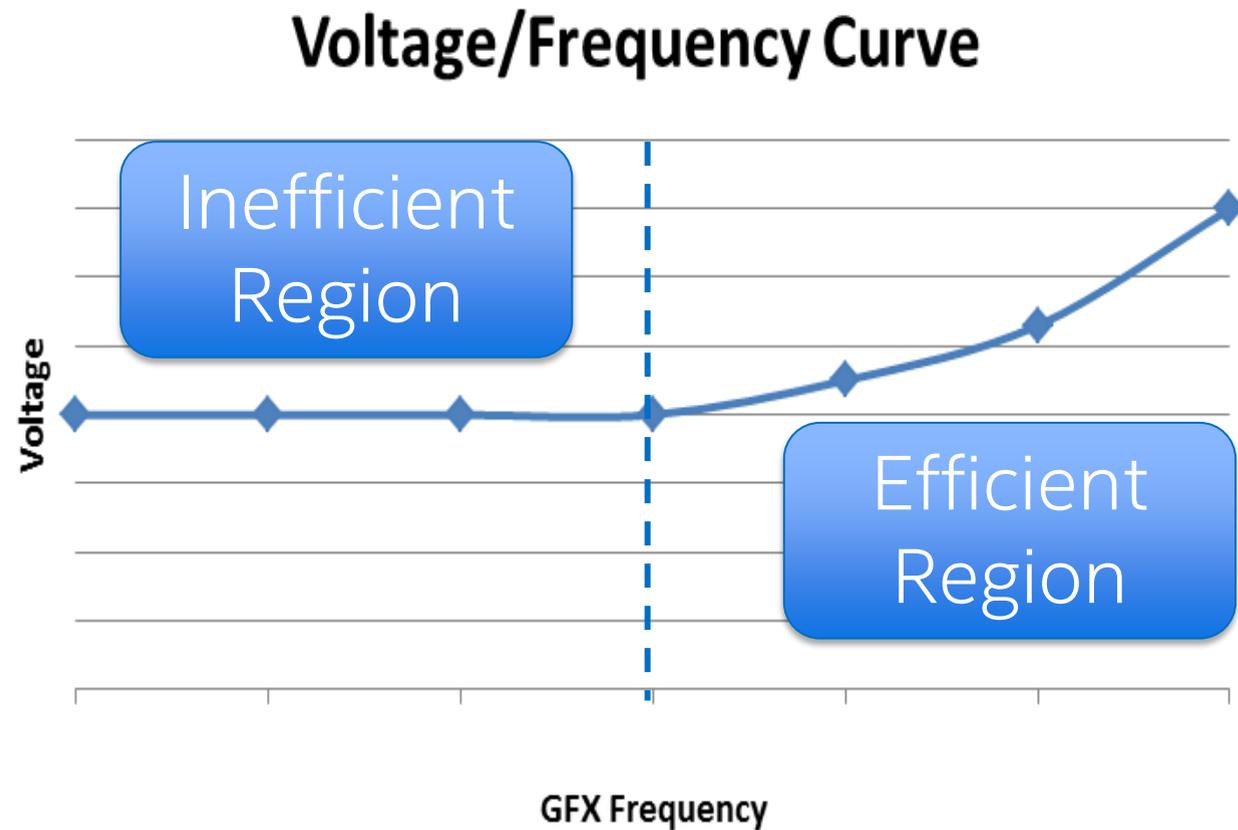
Active Power Reduction:

- Design Process co-optimization to reduce minimum operating voltage
- Optimized design methods for C_{dyn} reduction
- Major re-arch of DDR/IO/PLL/Graphics
- Micro-architecture optimizations for C_{dyn} reduction in IA, Graphics and PCH
- IA/GT/Cache Lower Operating Frequency Range
- Other algorithmic enhancements (E.g. Dynamic Display voltage resolution)

Leakage Power Reduction:

- Design Process co-optimization to reduce minimum operating voltage
- Lowered T_{jmax} to reduce voltage

Extending the Efficient Operating Range



- DCC: Duty Cycle Control
- Implemented with HW & graphics driver collaboration

Intel® Core™ M Processor Improvements



Enables $\leq 9\text{mm}$ Fanless 2-in1's for the First Time on the Intel Core™ Roadmap



Greater than 2X reduction in TDP with better performance vs. Haswell-Y



50% Smaller Package (XY), 30% Thinner



60% Lower SOC Idle Power for Increased Battery Life

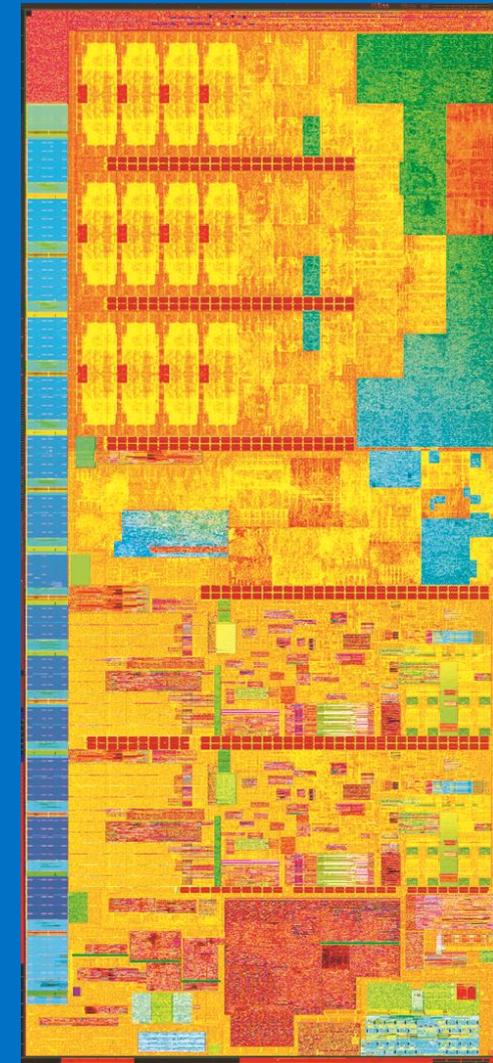
Agenda: Broadwell Micro-architecture

The Fanless Challenge

The Journey to Fanless

Broadwell Converged Core Improvements

Graphics/Media/Display



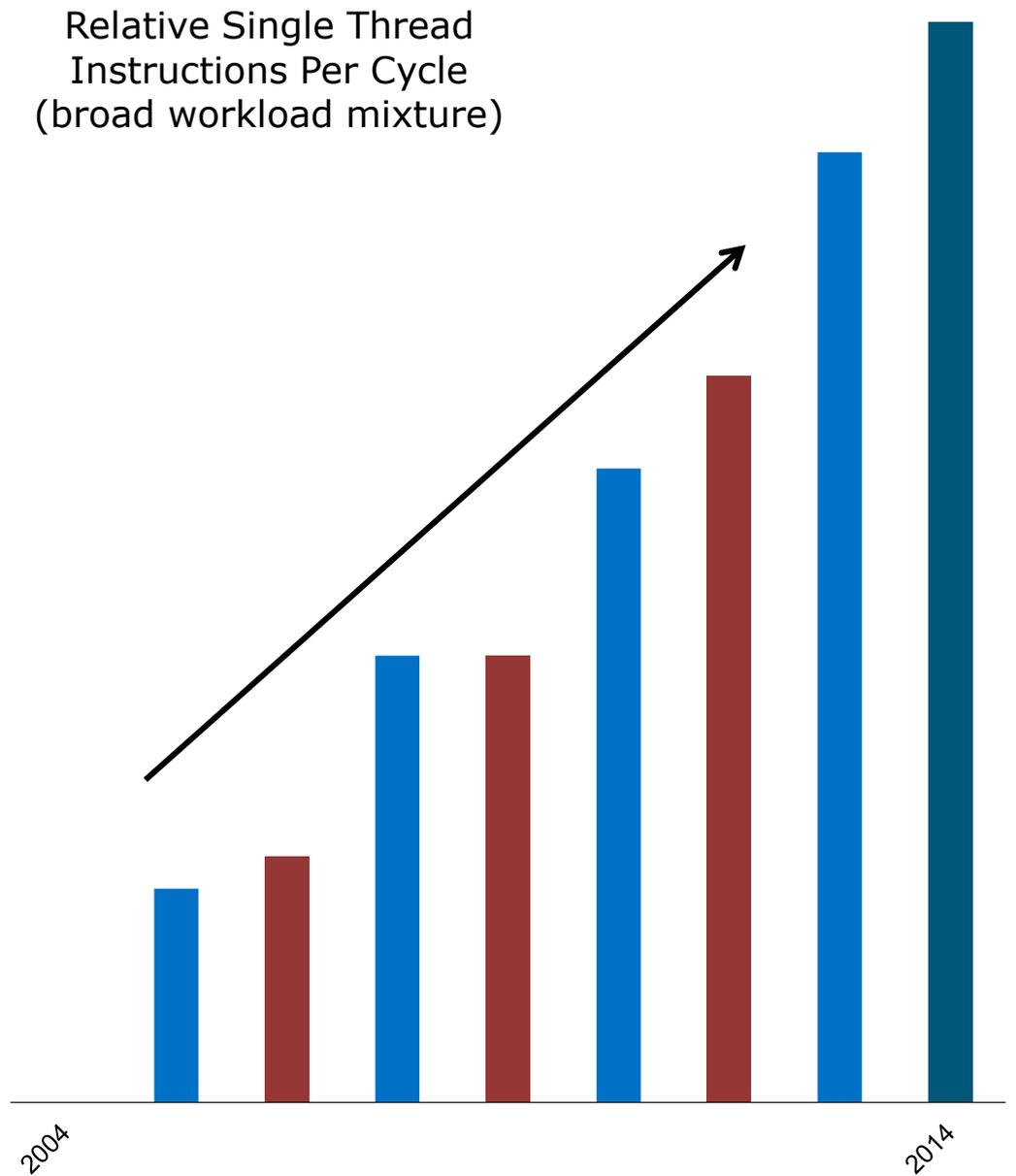
Broadwell Converged-Core

>5% IPC over Haswell

- Larger out-of-order scheduler, Faster store-to-load forwarding
- Larger L2 TLB (1K to 1.5K entries), new dedicated 1GB Page L2 TLB (16 entries)
- 2nd TLB page miss handler for parallel page walks
- Faster floating point multiplier (5 to 3 cycles), Radix-1,024 divider, faster vector Gather
- Improved address prediction for branches and returns
- Targeted cryptography acceleration instruction improvements
- Faster virtualization round-trips

Power efficiency

- Performance features designed at ~2:1 Performance:Power ratio
- Power gating and design optimization increase efficiency at every operating point



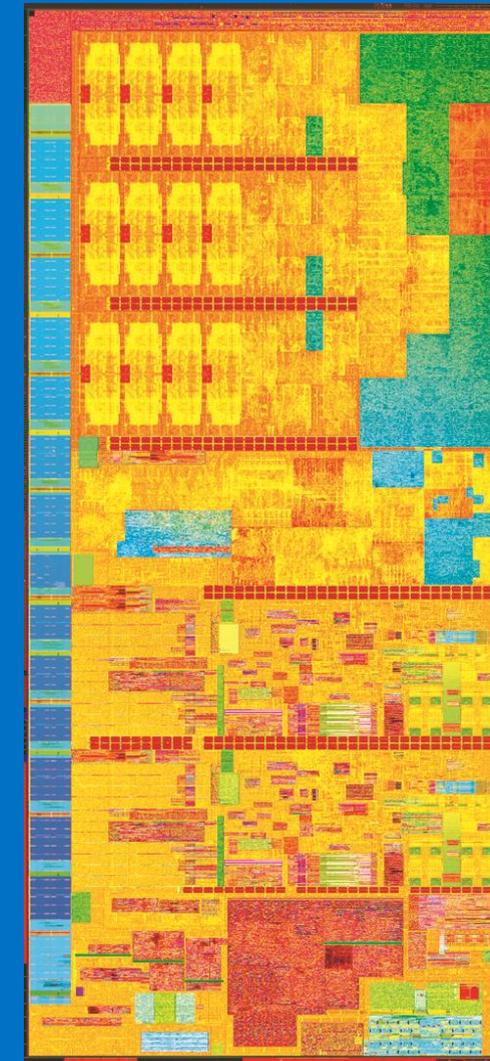
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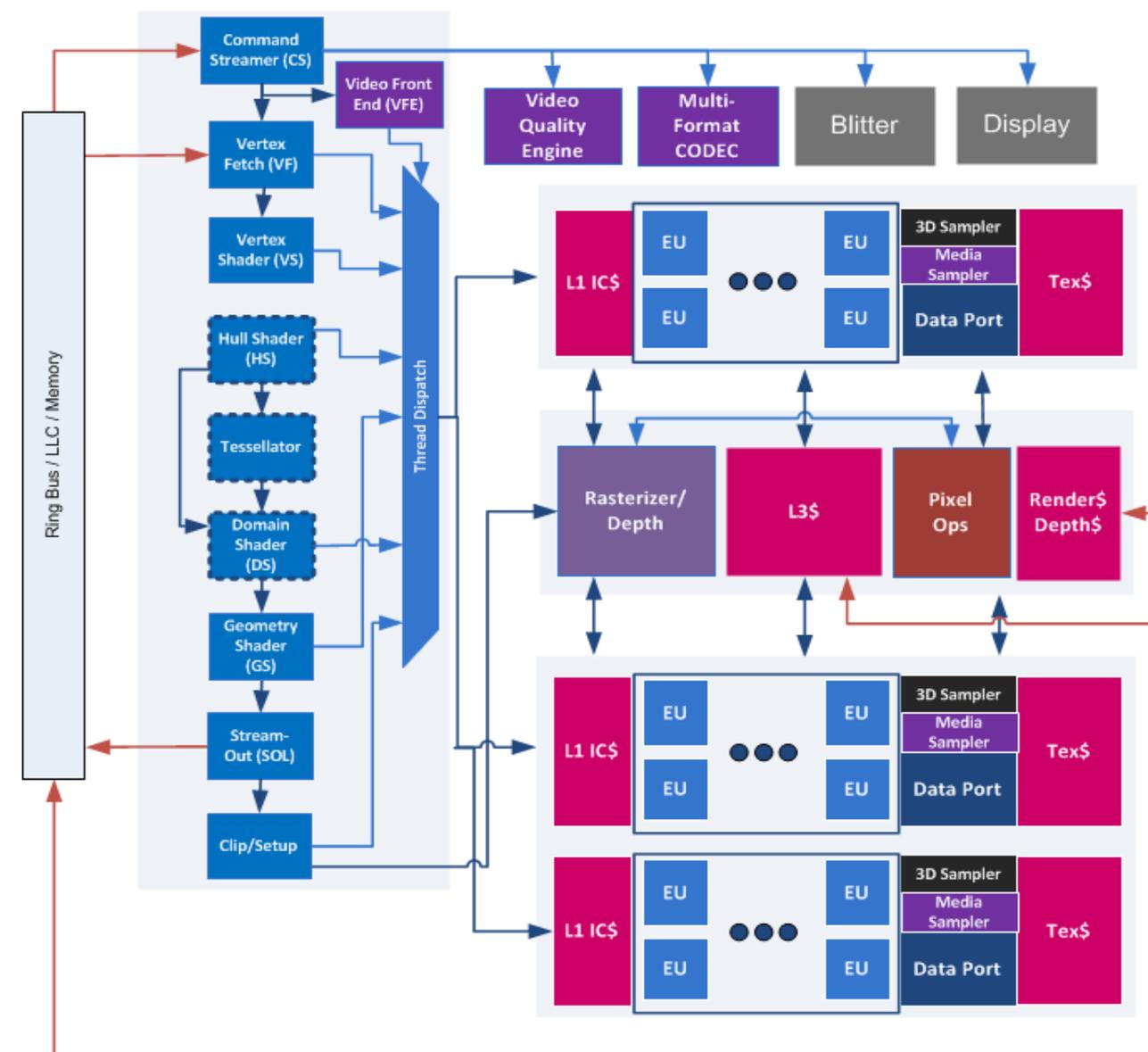
Broadwell Graphics Architecture Provides Faster 3D and Compute Performance

3D / Compute Architectural Enhancements

- 20% More Computes and 50% Higher Sampler Throughput
- Microarchitecture improvements for Increased Geometry, Z, Pixel Fill Performance
- More Thermal Headroom with 14nm Process
- Scalable Architecture

Software Enhancements

- Continued Focus on Gaming with support for Direct X* 11.2 & OpenGL* 4.3
- OpenCL 1.2 and 2.0 (with Shared Virtual Memory support) for GPU compute



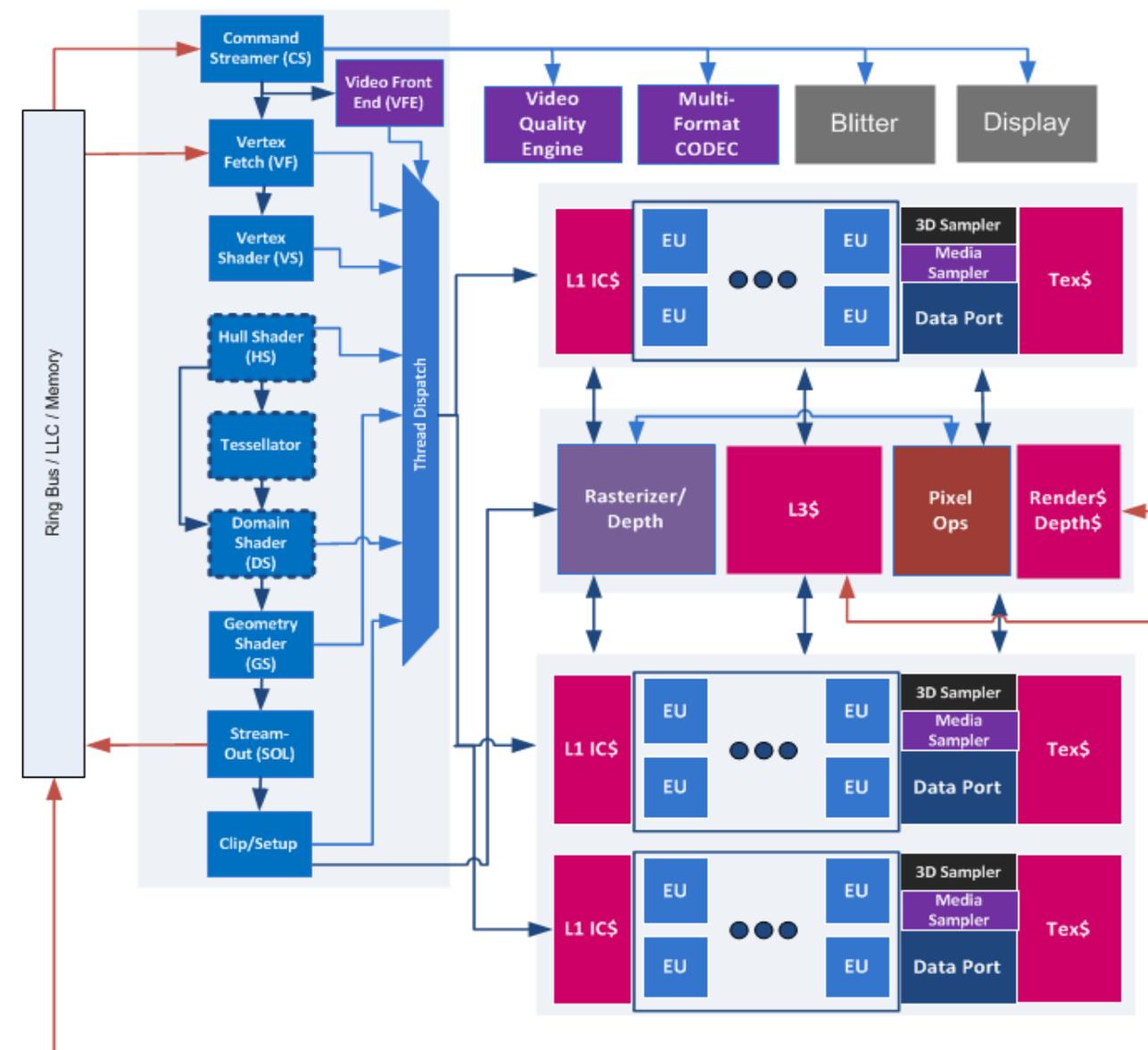
Broadwell Graphics Architecture Provides End-to-End 4K Media Experience

Media Architecture Enhancements

- 50% more Media Sampler plus 20% more compute
- Up to 2x Video Quality Engine throughput
- Continued quality and performance improvement for Intel™ Quick Sync Video Technology.
- Significant power reduction (thus longer battery) provided by the energy efficient 14nm process

Display Technology

- Native support for 4K and UHD resolutions
- Improved SoC level power reduction and DPST



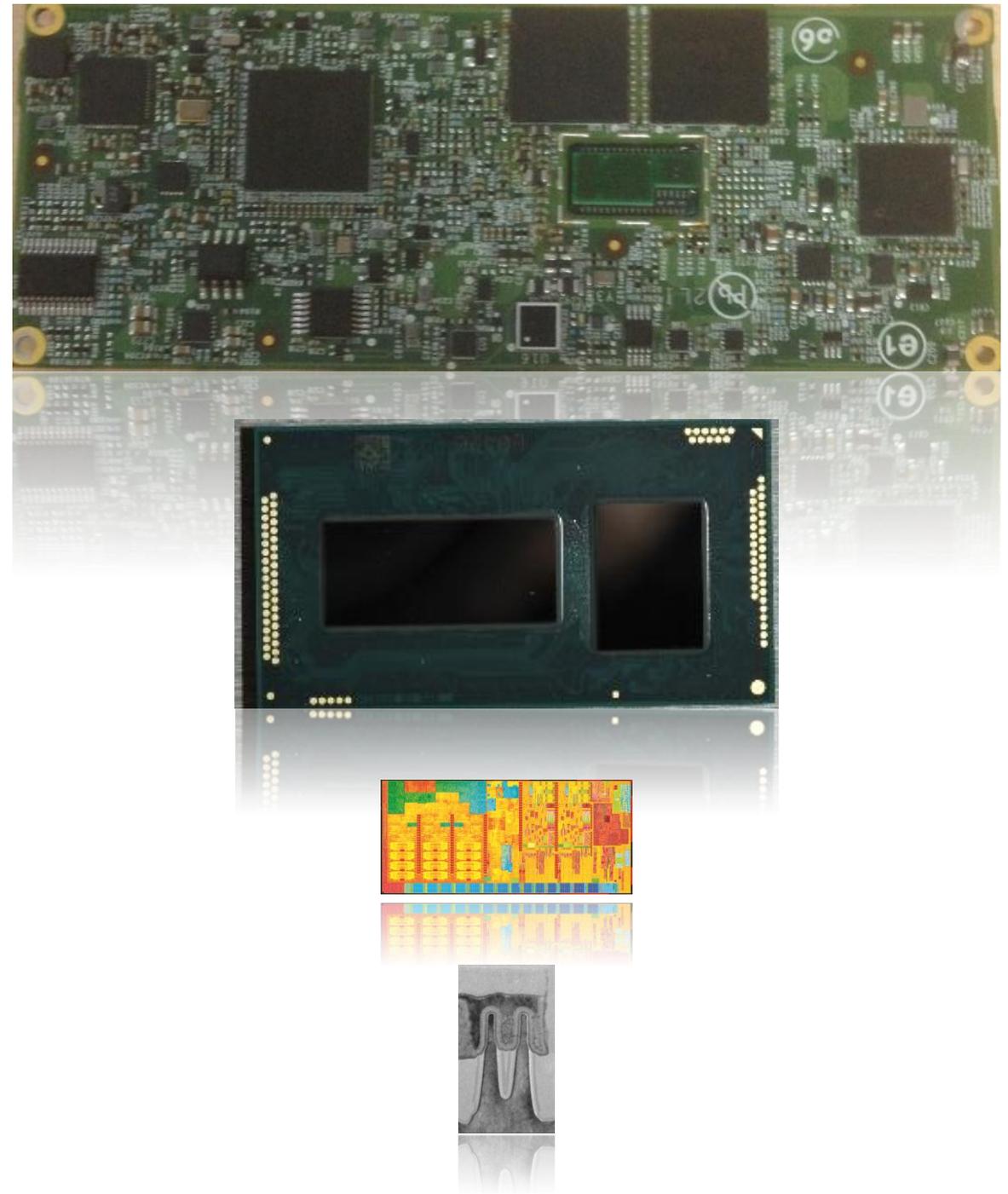
Key Messages

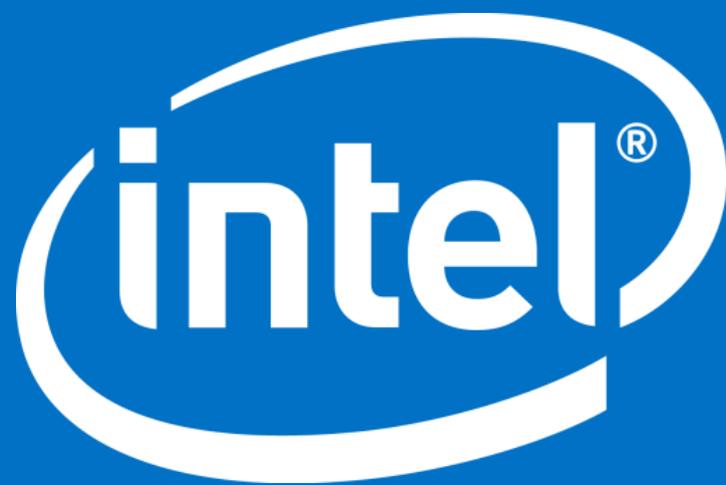
Multi-year journey to exciting products

14nm provided a tremendous advantage

Embracing outside-in system design

Intel is furiously delivering on our vision
with compelling products!





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- Relative performance for each benchmark is calculated by taking the actual benchmark result for the first platform tested and assigning it a value of 1.0 as a baseline. Relative performance for the remaining platforms tested was calculated by dividing the actual benchmark result for the baseline platform into each of the specific benchmark results of each of the other platforms and assigning them a relative performance number that correlates with the performance improvements reported.
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